



*Los Alamos New Mexico  
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# ***The Dynamic Interplay Between Spacecraft Charging, Space Environment Interactions and Evolving Materials***

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# Acknowledgements

## Support & Collaborations

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**JWST (GSFC/MSFC)**  
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**Solar Sails (JPL)**  
**AFRL**  
**Boeing**  
**Ball Aerospace**  
**Orbital**

**National Research  
Council**

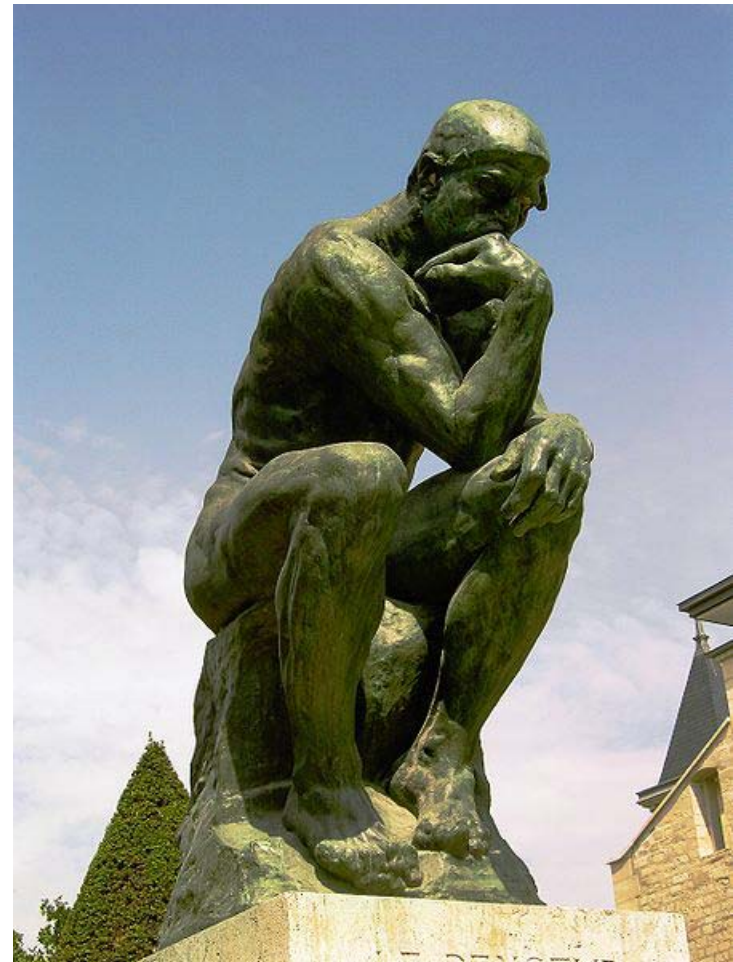


## USU Materials Physics Group

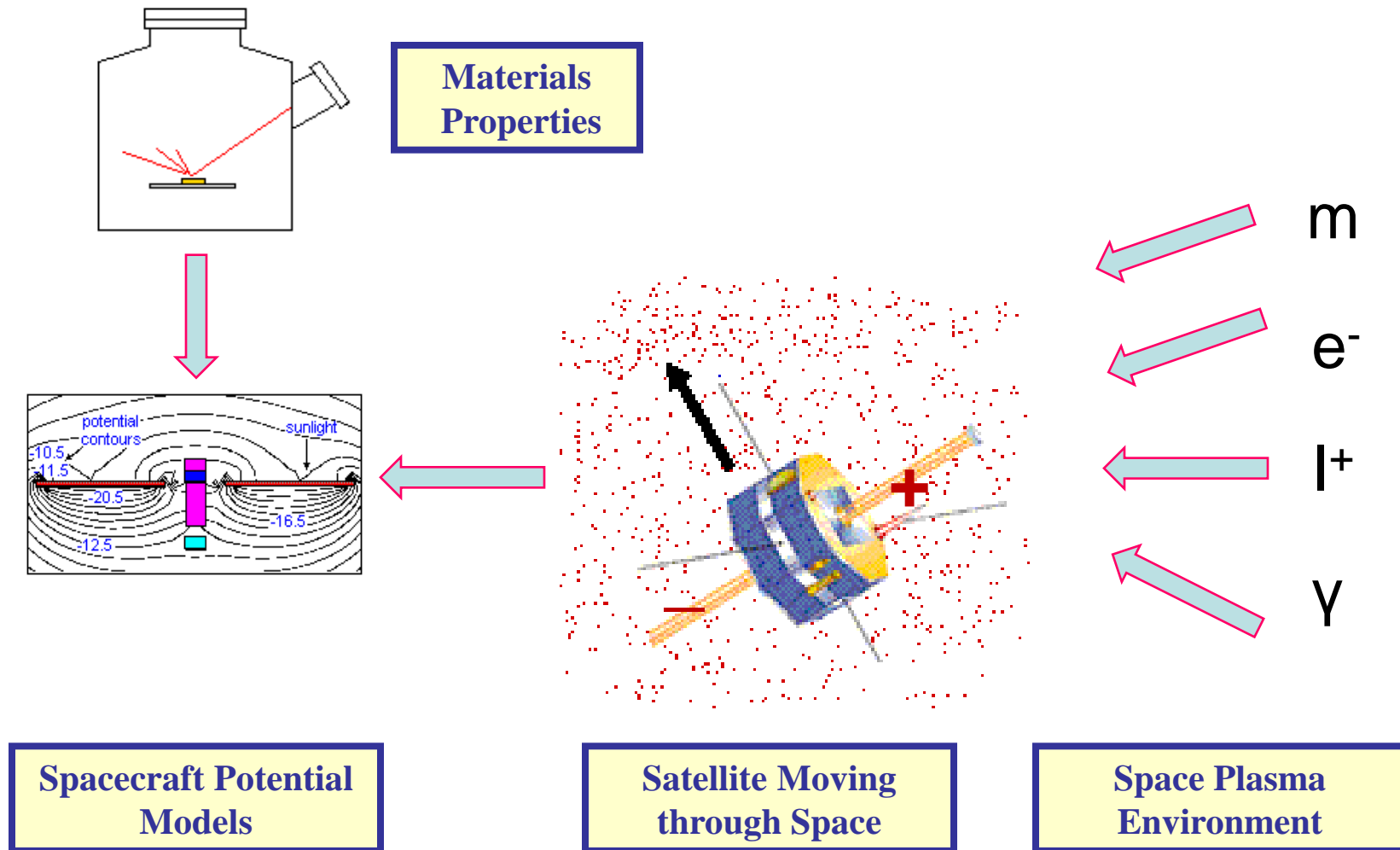
**Nothing endures  
but change.**

--Heraclitus of Ephesus  
(c. 495 BC)

***Shit Happens.....***

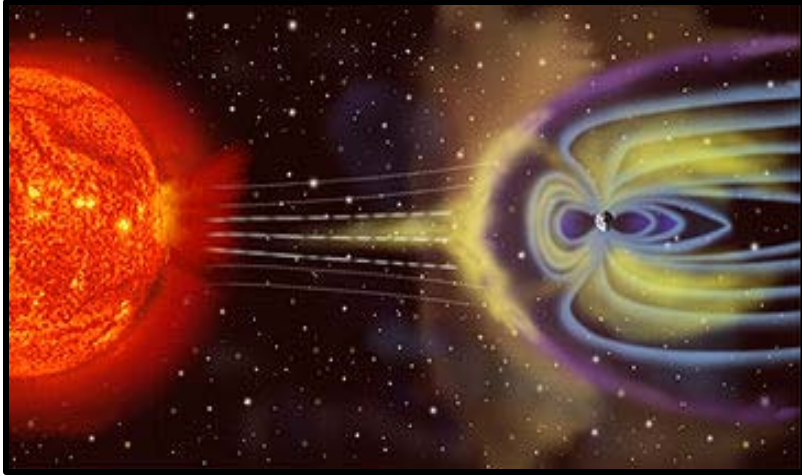


# A simplified approach to spacecraft charging modeling...

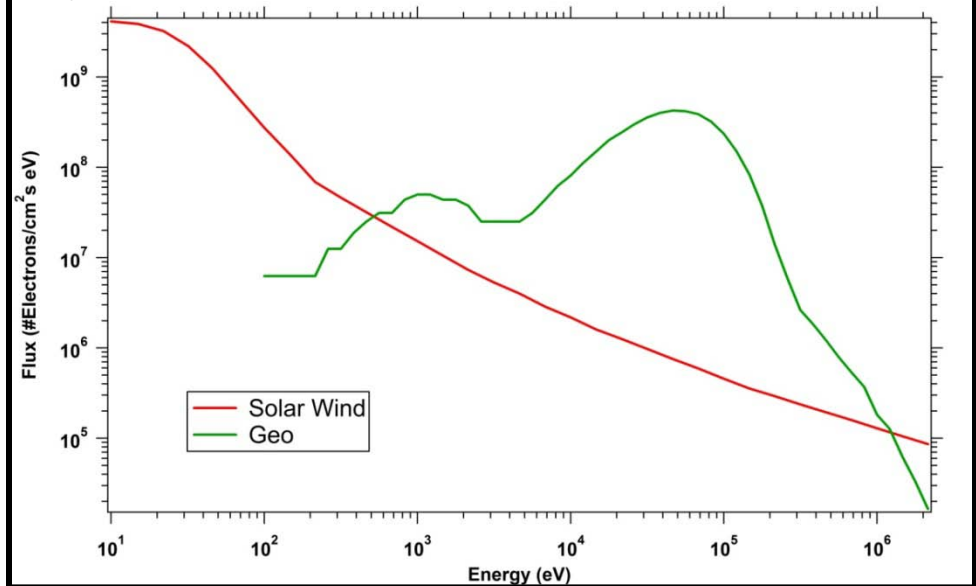




Solar wind and Earth's magento-sphere structure.



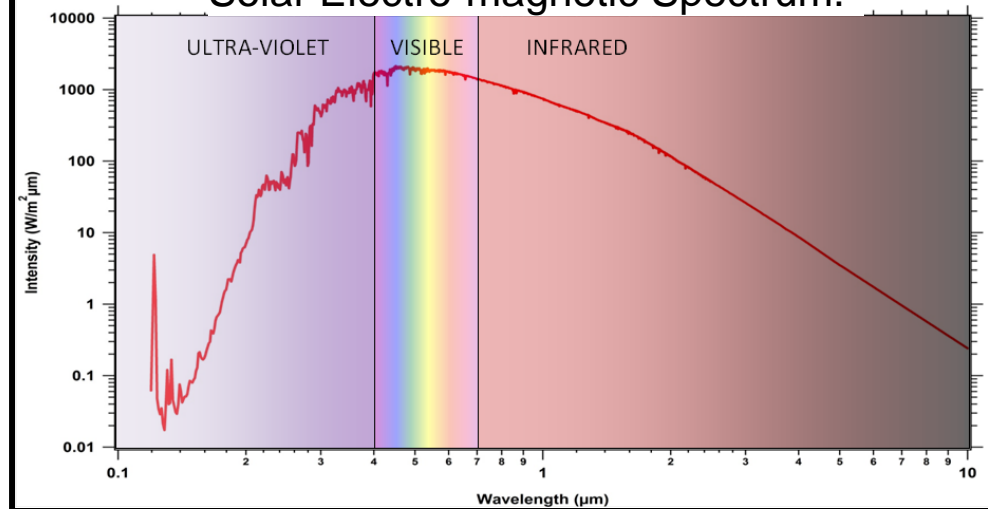
Typical Space Electron Flux Spectra [Larsen].



## Incident Fluxes of:

- **Electrons**
- **Ions**
- **Photons**
- **Particles**

Solar Electro-magnetic Spectrum.





# Dale Ferguson's "New Frontiers in Spacecraft Charging"

- #1 Non-static Spacecraft Materials Properties**
- #2 Non-static Spacecraft Charging Models**

**These result from the complex dynamic interplay between space environment, satellite motion, and materials properties**

**Specific focus of this talk is the change in materials properties as a function of time , position, energy, and charge:**

- **Time (Aging),  $t$**
- **Energy**
  - **Temperature,  $k_B T$**
  - **Deposited Energy (Dose),  $D$**
  - **Energy Deposition (Dose) Rate,  $\dot{D}$**
- **Charge**
  - **Accumulated Charge,  $\Delta Q$  or  $\Delta V$**
  - **Charge Profiles,  $Q(z)$**
  - **Charge Rate (Current),  $\dot{Q}$**
  - **Conductivity Profiles,  $\sigma(z)$**

# What do you need to know about the materials properties?

Charging codes such as NASCAP-2K or SPENVIS and NUMIT2 or DICTAT require:

## Charge Accumulation

- **Electron yields**
- **Ion yields**
- **Photoyields**
- **Luminescence**

## Charge Transport

- **Conductivity**
- **RIC**
- **Dielectric Constant**
- **ESD**
- **Range**

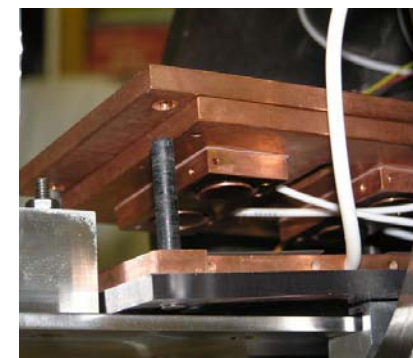
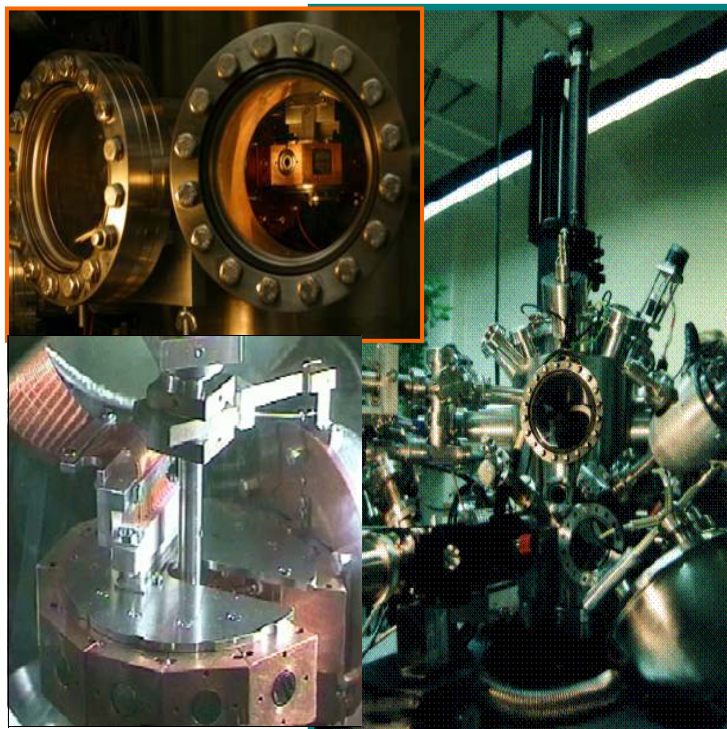
**ABSOLUTE** values as functions of materials species, flux, fluence, and energy.

Table 2.1. Parameters for NASCAP Materials Properties

Parameter	Value
[1] Relative dielectric constant; $\epsilon_r$ (Input as 1 for conductors)	1, NA
[2] Dielectric film thickness; d	0 m, NA
[3] Bulk conductivity; $\sigma_o$ (Input as -1 for conductors)	-1; $(4.26 \pm 0.04) \cdot 10^7 \text{ ohm}^{-1} \cdot \text{m}^{-1}$
[4] Effective mean atomic number $\langle Z_{\text{eff}} \rangle$	$50.9 \pm 0.5$
[5] Maximum SE yield for electron impact; $\delta_{\text{max}}$	$1.47 \pm 0.01$
[6] Primary electron energy for $\delta_{\text{max}}$ ; $E_{\text{max}}$	$(0.569 \pm 0.07) \text{ keV}$
[7] First coefficient for bi-exponential range law, $b_1$	1 Å, NA
[8] First power for bi-exponential range law, $n_1$	$1.39 \pm 0.02$
[9] Second coefficient for bi-exponential range law, $b_2$	0 Å
[10] Second power for bi-exponential range law, $n_2$	0
[11] SE yield due to proton impact $\delta^H(1\text{keV})$	$0.3364 \pm 0.0003$
[12] Incident proton energy for $\delta^H_{\text{max}}$ ; $E^H_{\text{max}}$	$(1238 \pm 30) \text{ keV}$
[13] Photoelectron yield, normally incident sunlight, $j_{\text{pho}}$	$(3.64 \pm 0.4) \cdot 10^{-5} \text{ A} \cdot \text{m}^{-2}$
[14] Surface resistivity; $\rho_s$ (Input as -1 for non-conductors)	-1 ohms·square <sup>-1</sup> , NA
[15] Maximum potential before discharge to space; $V_{\text{max}}$	10000 V, NA
[16] Maximum surface potential difference before dielectric breakdown discharge; $V_{\text{punch}}$	2000 V, NA
[17] Coefficient of radiation-induced conductivity, $\sigma_r$ ; k	0 ohms <sup>-1</sup> ·m <sup>-1</sup> , NA
[18] Power of radiation-induced conductivity, $\sigma_r$ ; $\Delta$	0, NA

## Absolute Yields

- SEE, BSE, emission spectra , (<20 eV to 30 keV)
- Angle resolved electron emission spectra
- Photoyield (~160 nm to 1200 nm)
- Ion yield (He, Ne, Ar, Kr, Xe; <100 eV to 5 keV)
- Cathodoluminescence (200 nm to 5000 nm)
- No-charge “Intrinsic” Yields
- T (<40 K to >400 K)



- Conductivity (<10<sup>-22</sup> [ohm-cm]<sup>-1</sup>)
- Surface Charge (<1 V to >15 kV)
- ESD (low T, long duration)
- Radiation Induced Conductivity (RIC)
- Multilayers, contamination, surface modification
- Radiation damage
- Sample Characterization



# **“New Frontiers” from a Materials Perspective**

## **Consider 6 Cases of Dynamical Change in Materials:**

- I. Contamination and Oxidation**
- II. Surface Modification**
- III. Radiation Effects (and  $t$ )**
- IV. Temperature Effects (and  $t$ )**
- V. Radiation and Temperature Effects**
- VI. Multilayer/Nanocomposite Effects**

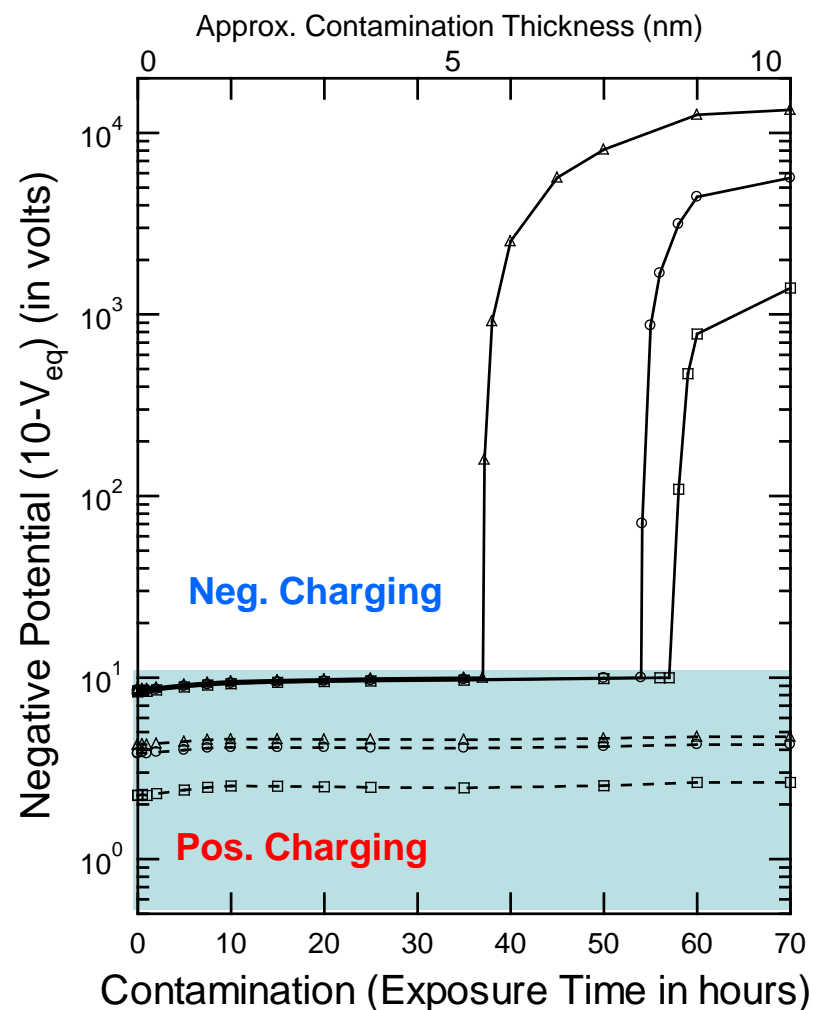
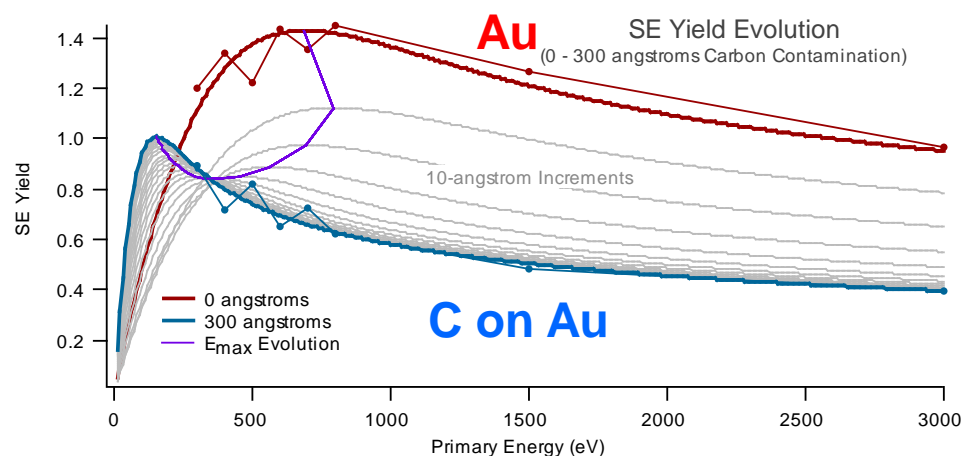


# Case I: Evolution of Contamination and Oxidation

“All spacecraft surfaces are eventually carbon...”

--C. Purvis

This led to lab studies by Davies, Kite, and Chang



# Case I: Evolution of Contamination and Oxidation

## Wake Side

- 13 Grounded Samples
- 12 Biased Samples: for 3 sets of 4 samples with low current biases for charge-enhanced contamination studies.

- 6 Concealed Samples

## Sample Holders

- Holder area 5 cm x 15 cm
- 9 mm diameter exposed sample area

Grounded Guard Plate

-5 VDC

+5 VDC

-15 VDC

Before

After

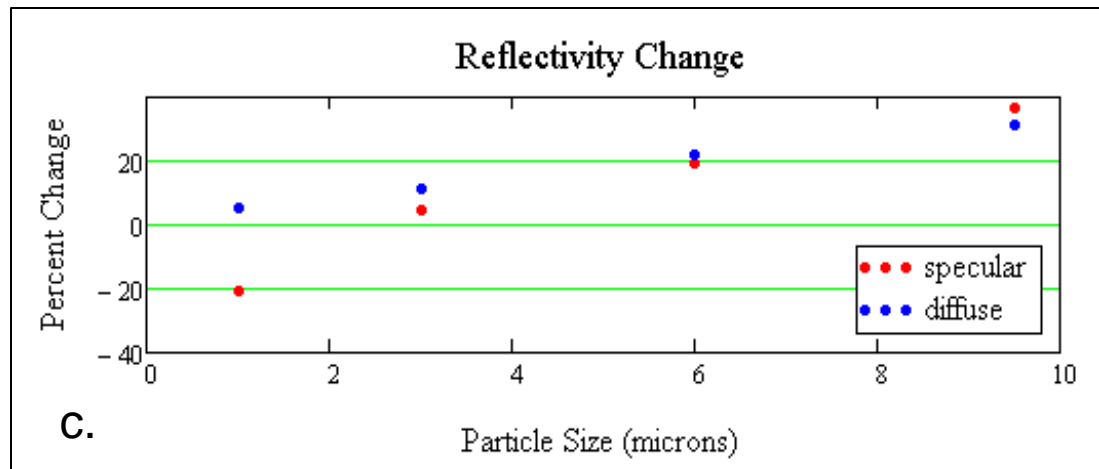
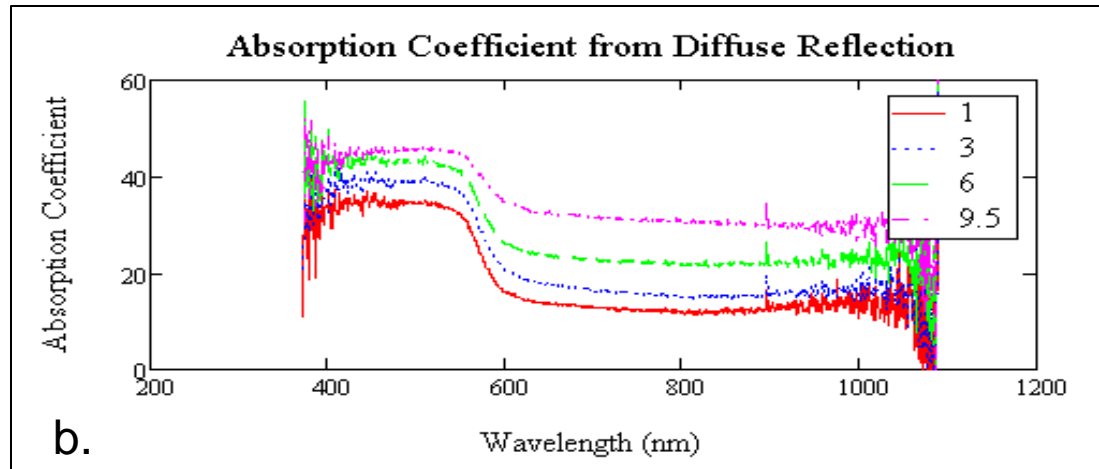
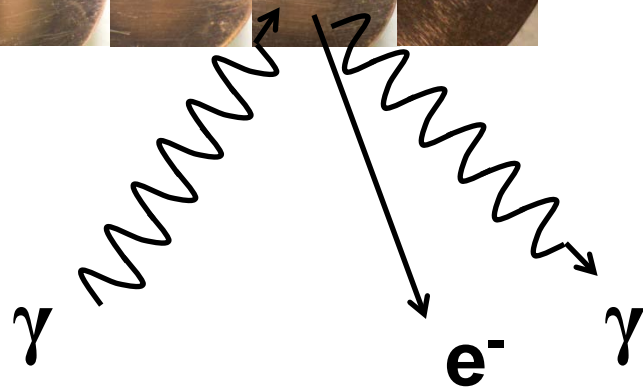
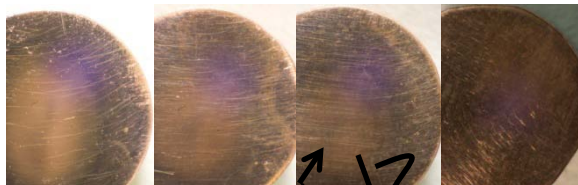
**SUSpECs on MISSE-6**

Ag coated Mylar with micrometeoroid impact  
See poster by Dennison, Evans and Prebola

# Case II: Surface Modification

**Diffuse and Specular Reflectivity changes with surface roughness**

**Successive stages of roughened Cu**



**View photon (electron) scattering as a competition for deposited energy and charge:**

- Reflectivity— $\gamma$  out (Luminescence— $\gamma$  out)
- Photoyield— $e^-$  out (SE/BSE— $e^-$  out)

# Cases I and II: Reflectivity as a Feedback Mechanism

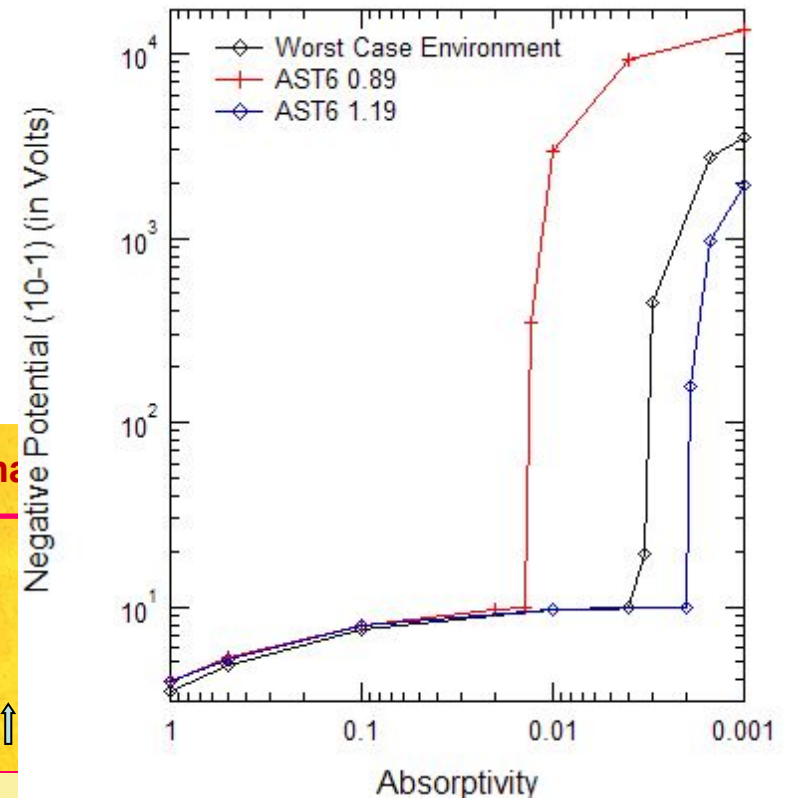
Reflectivity changes with surface roughness and contamination

Reflect → Charging → Contamination

Reflect → Emissivity → Temp → Contamination

Charging → Reflectivity

Radiation → Reflect → Emissivity → Temp → Contamination



Radiation Damage (Color Change) of Tedlar

B. Mihaljcic in Guild's 11<sup>th</sup> SCTS Talk

See Lai & Tautz, 2006 & Dennison 2007  
JWST Structure: Charging vs. Ablation

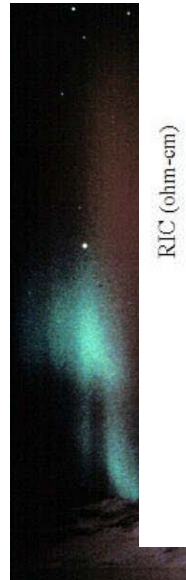


# Case III: Radiation Effects

Large Dosage ( $>10^8$  Rad)

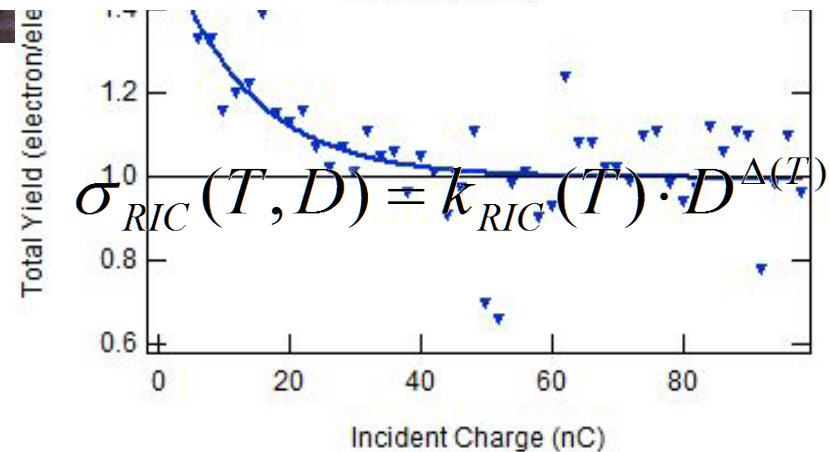
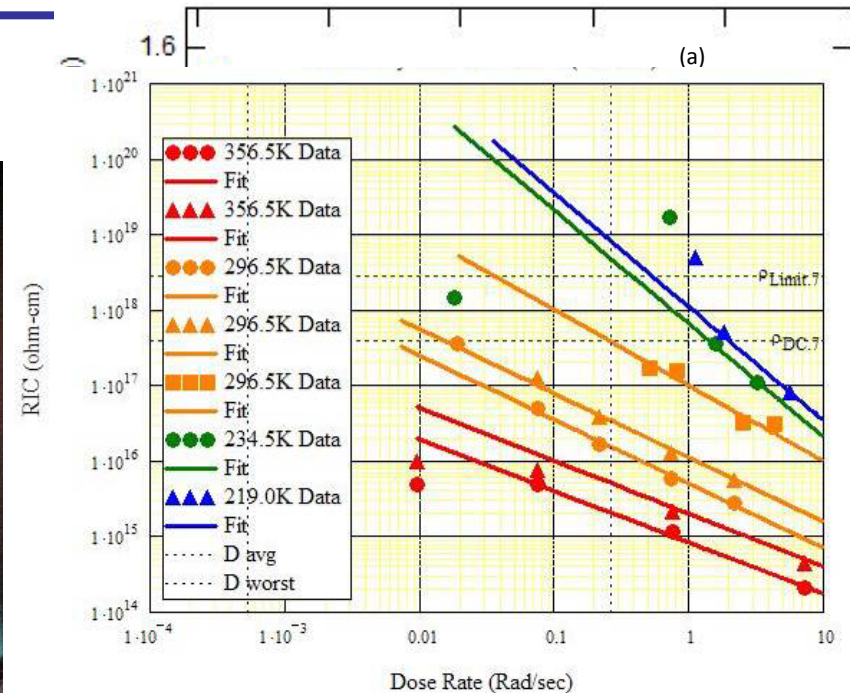
Medium Dosage ( $>10^7$  Rad)

Low Dose Rate ( $>10^0$  Rad/s)



“...Earth is for Wimps...” H. Garrett

Examples:  
 Examples: RBSP, MMS, JUNO, JGO/JEO  
 “...auroral fields may cause significant  
 Radiation induced Conductivity  
 Mechanical Modification of Electron  
 (RIC)  
 Transport and Emission Properties  
 Examples: RBSP, JUNO, JGO/JEO  
 Caused by bondbreaking and trap creation  
 (see A Sim poster)  
 Mechanical and Optical Materials Damage  
 (see Hoffmann & A Sim posters)





## Strong T Dependence for Insulators

### Charge Transport

- Conductivity
- RIC
- Dielectric Constant
- ESD

## Examples:

### **IR and X-Ray Observatories**

JWST, WISE, WMAP, Spitzer,  
Herscel, IRAS, MSX, ISO,  
COBE, Planck

### ***Outer Planetary Mission***

Galileo, Juno, JEO/JGO.  
Cassini, Pioneer, Voyager,

### ***Inner Planetary Mission***

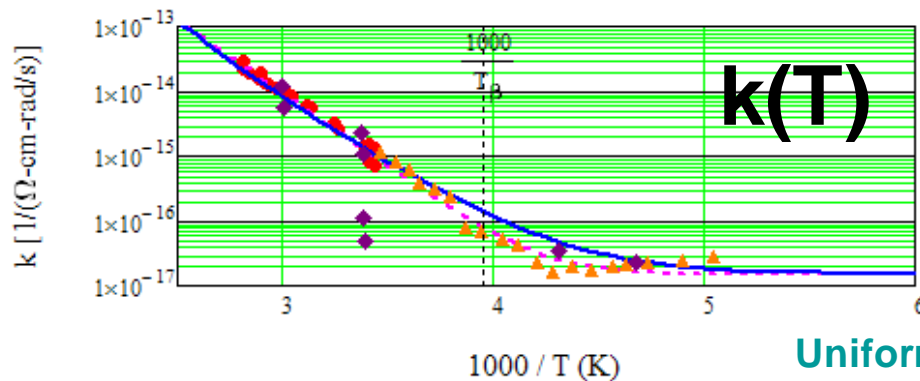
SPM, Ulysses, Magellan,  
Mariner

# Case IV: Temperature Effects

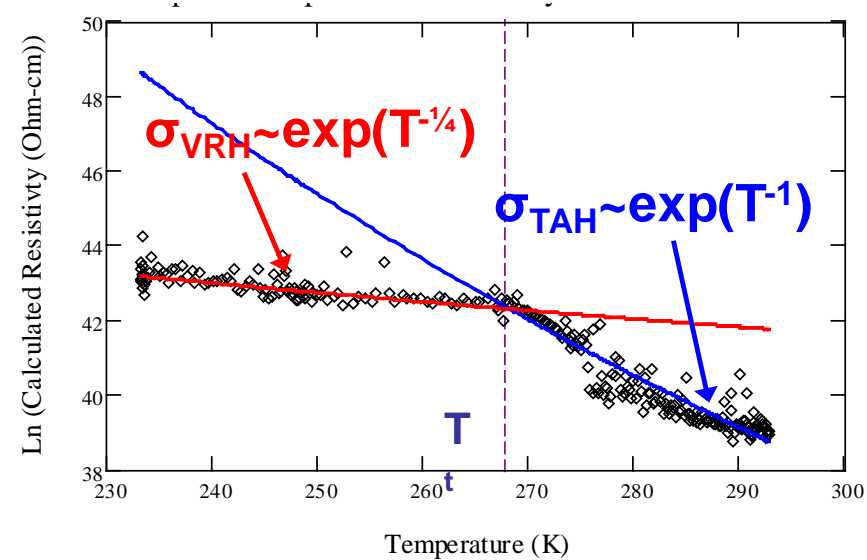
## Strong T Dependence for Insulators

### Charge Transport

- Conductivity
- RIC
- Dielectric Constant
- ESD



- Yagahi, 1963 Data
- - - Exponential Fit
- Power Law Fit
- ▲▲▲ Fowler, 1956 Data
- ◆◆ USU Data



### Uniform Trap Density

$$\Delta(T) \rightarrow 1$$

$$k(T) \rightarrow k_{RICo}$$

$$\sigma_{RIC}(T, D) = k_{RIC}(T) \cdot D^{\Delta(T)}$$

### Exponential Trap Density

$$\Delta(T) \rightarrow \frac{T_c}{T + T_c}$$

$$k(T) \rightarrow k_{RIC1} \left[ 2 \left( \frac{m_e k_B T}{2\pi \hbar^2} \right)^{3/2} \left( \frac{m_e^* m_h^*}{m_e m_e} \right)^{3/4} \right]^{\frac{T}{T+T_c}}$$

# Case IV: Temperature Effects—JWST

## JWST

### **Very Low Temperature**

Virtually all insulators go to infinite resistance—perfect charge integrators

### **Long Mission Lifetime (10-20 yr)**

No repairs

Very long integration times

### **Large Sunshield**

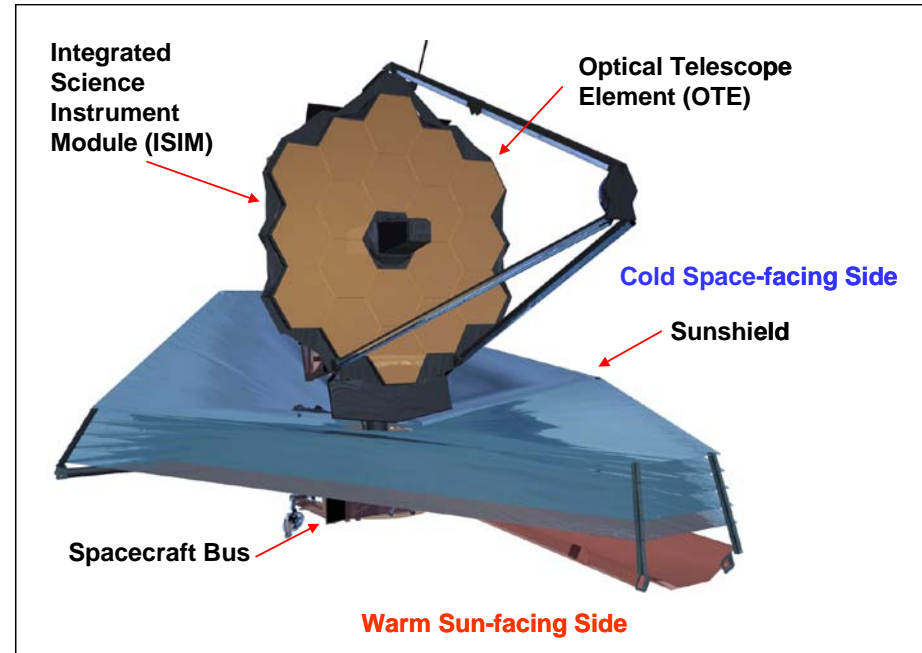
Large areas

Constant eclipse with no photoemission

### **Large Open Structure**

Large fluxes

Minimal shielding



### **Variation in Flux**

Large solar activity variations

In and out of magnetotail

### **Complex, Sensitive Hardware**

Large sensitive optics

Complex, cold electronics

# Case V: Temperature and Dose Effects

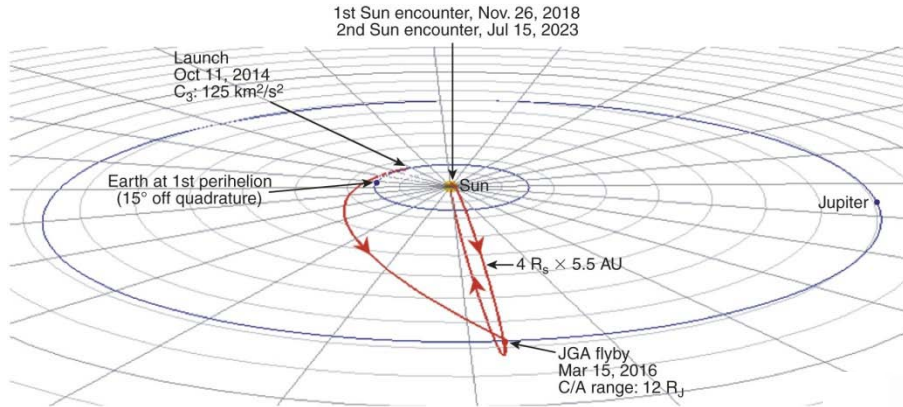


Figure 4-1. Solar Probe mission summary.

**Wide Orbital Range**  
**Earth to Jupiter Flyby**  
**Solar Flyby to  $4 R_S$**

**Wide Temperature Range**  
**<100 K to >1800 K**

**Wide Dose Rate Range**  
**Five orders of magnitude variation!**

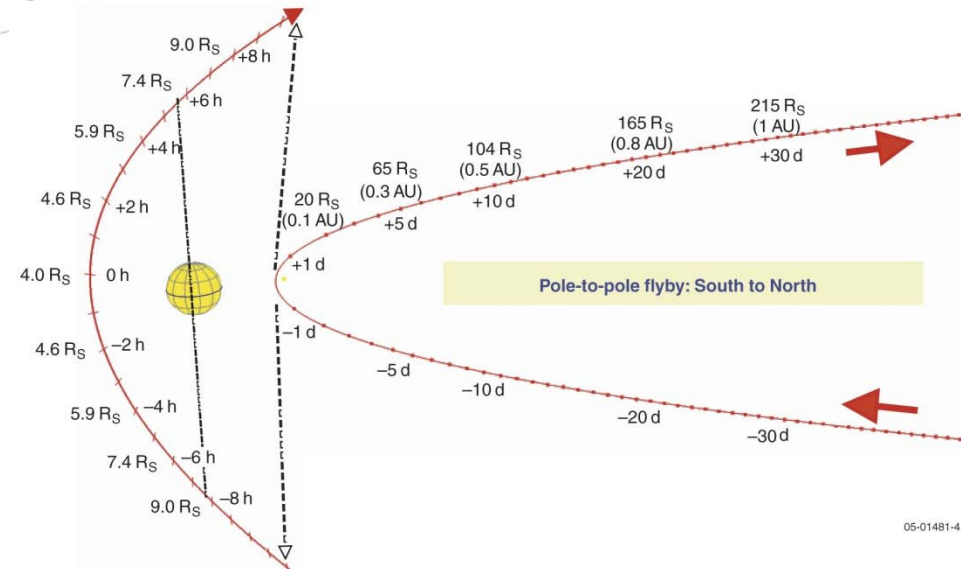
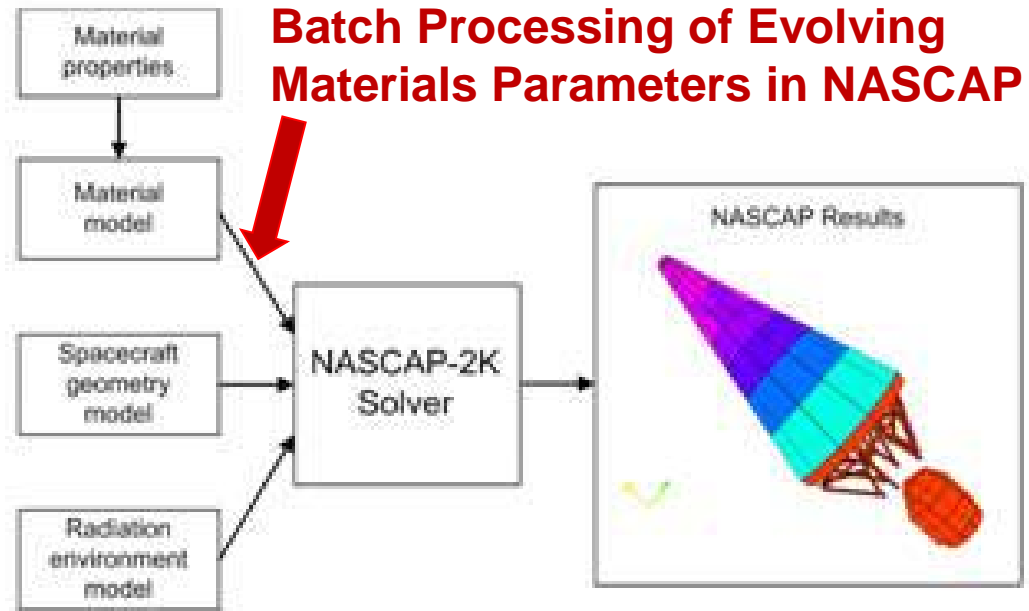


Figure 4-2. Solar encounter trajectory and timeline. Science operations begin at perihelion —5 days ( $65 R_S$ ) and continue until perihelion +5 days.

# Case V: Temperature and Dose Effects

“We anticipate significant thermal and charging issues.”

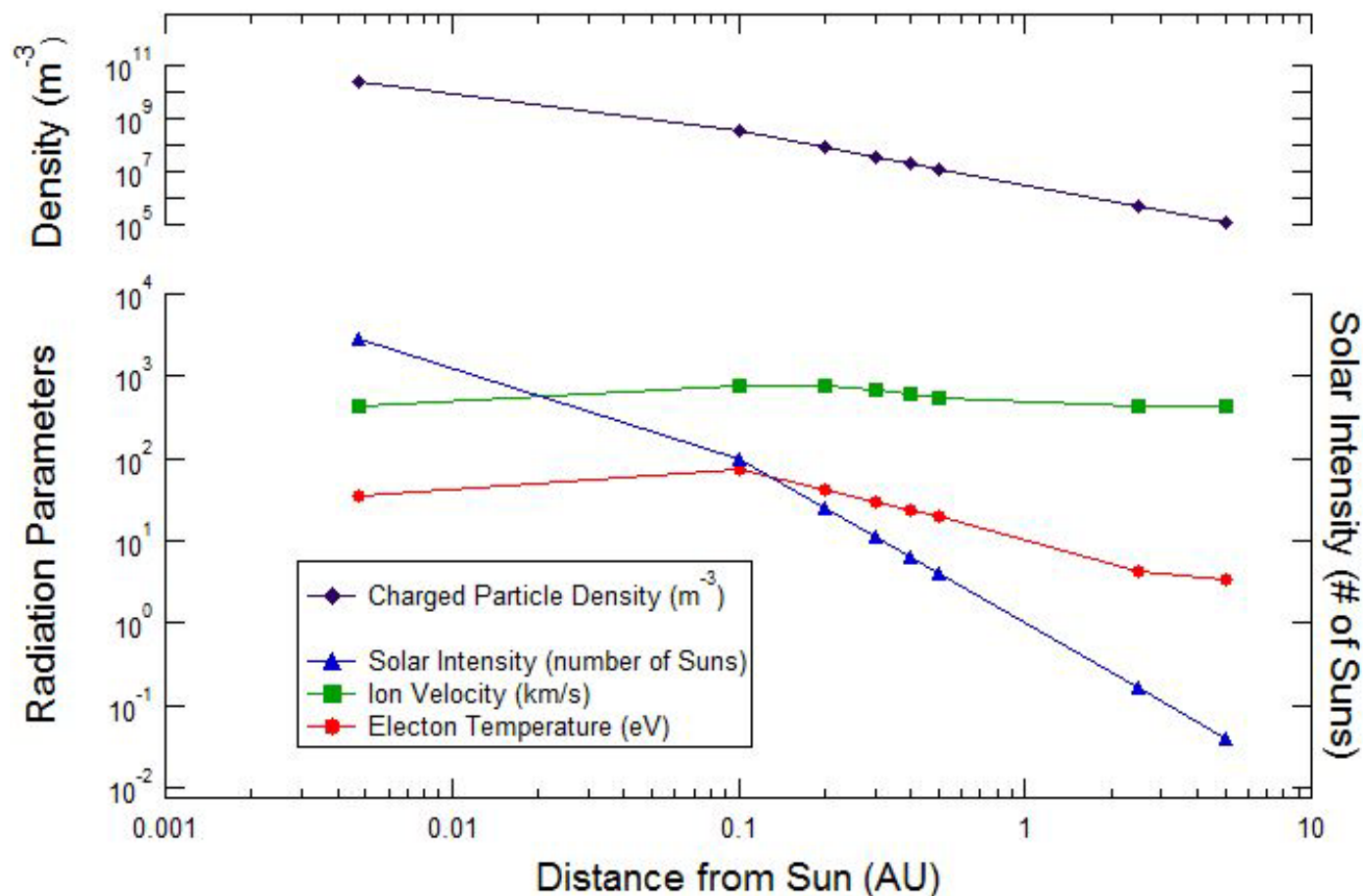
*J. Sample*



- *Mission design by APL/GSFC*
- *Materials testing by Dennison and Hoffmann*
- *Evolutionary Charging Study by Donegan, Sample, Dennison & Hoffmann*  
(See Donegann et al, JSR 2009)
- *Revised mission design and new charging study*  
(See Donegann 11<sup>th</sup> SCTC Poster for update)



# Case V: Temperature and Dose Effects



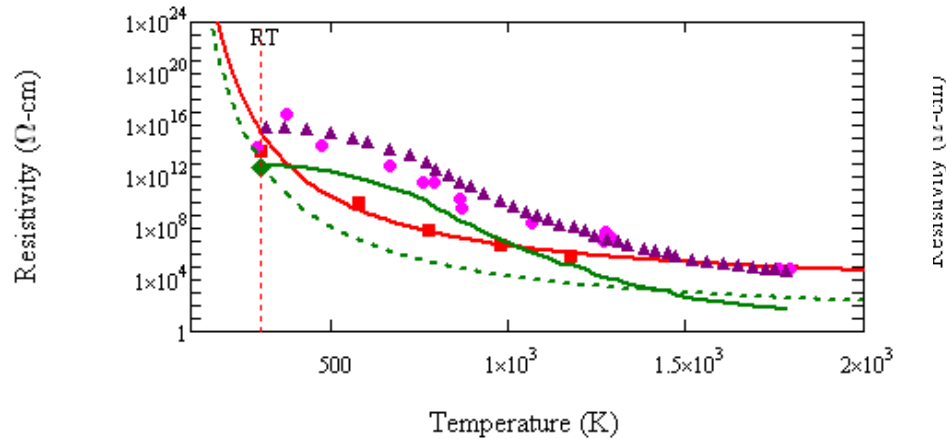
**Wide Orbital Range**  
 Earth to Jupiter Flyby  
 Solar Flyby to  $4 R_s$

**Wide Temperature Range**  
 $<100 \text{ K}$  to  $>1800 \text{ K}$

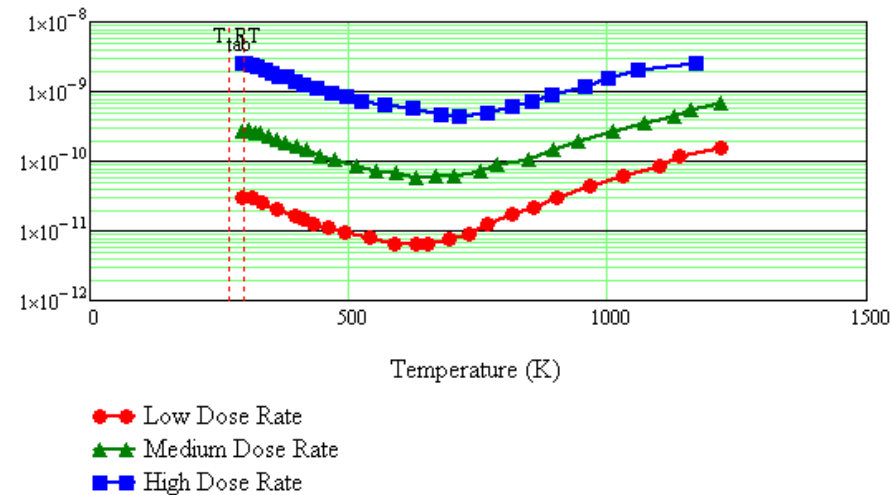
**Wide Dose Rate Range**  
 Five orders of magnitude variation!

# Case V: Temperature and Dose Effects

## Dark Conductivity vs T



## RIC vs T



## Dark Conductivity

$$\sigma_{DC}(T) = \sigma_o^{DC} e^{-E_o/k_B T}$$

## RIC

$$\sigma_{RIC}(T) = k_{RIC}(T) \dot{D}^{\Delta(T)}$$

## Dielectric Constant

$$\epsilon_r(T) = \epsilon_{RT} + \Delta_\epsilon(T - 298 K)$$

## Electrostatic Breakdown

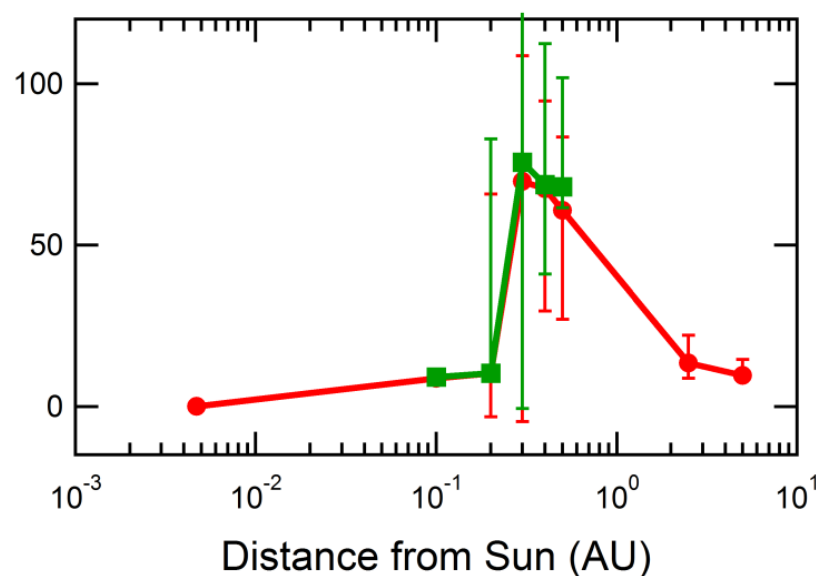
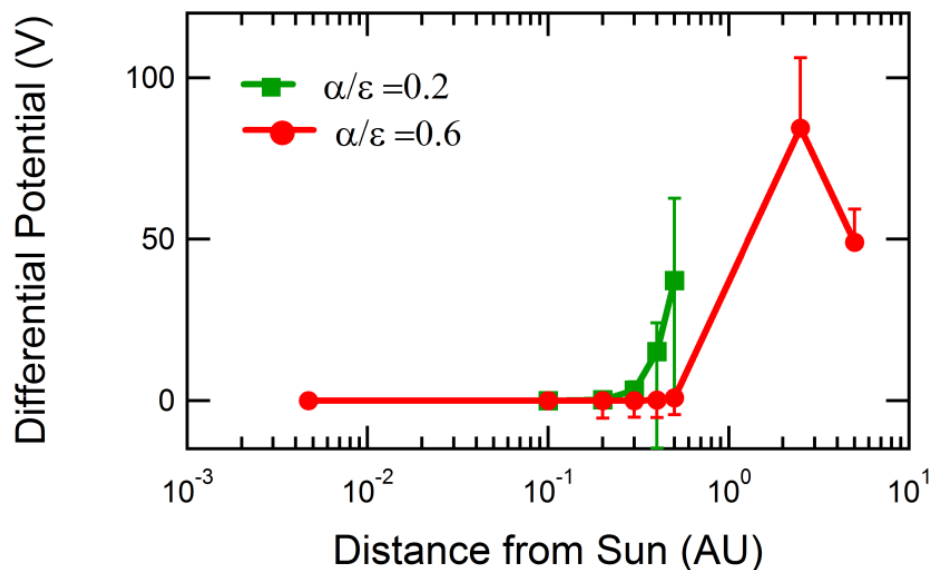
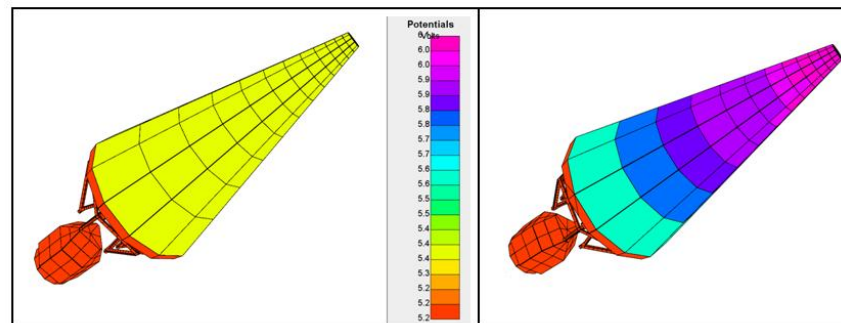
$$E_{ESD}(T) = E_{ESD}^{RT} e^{-\alpha_{ESD}(T - 298 K)}$$

# Case V: Temperature and Dose Effects

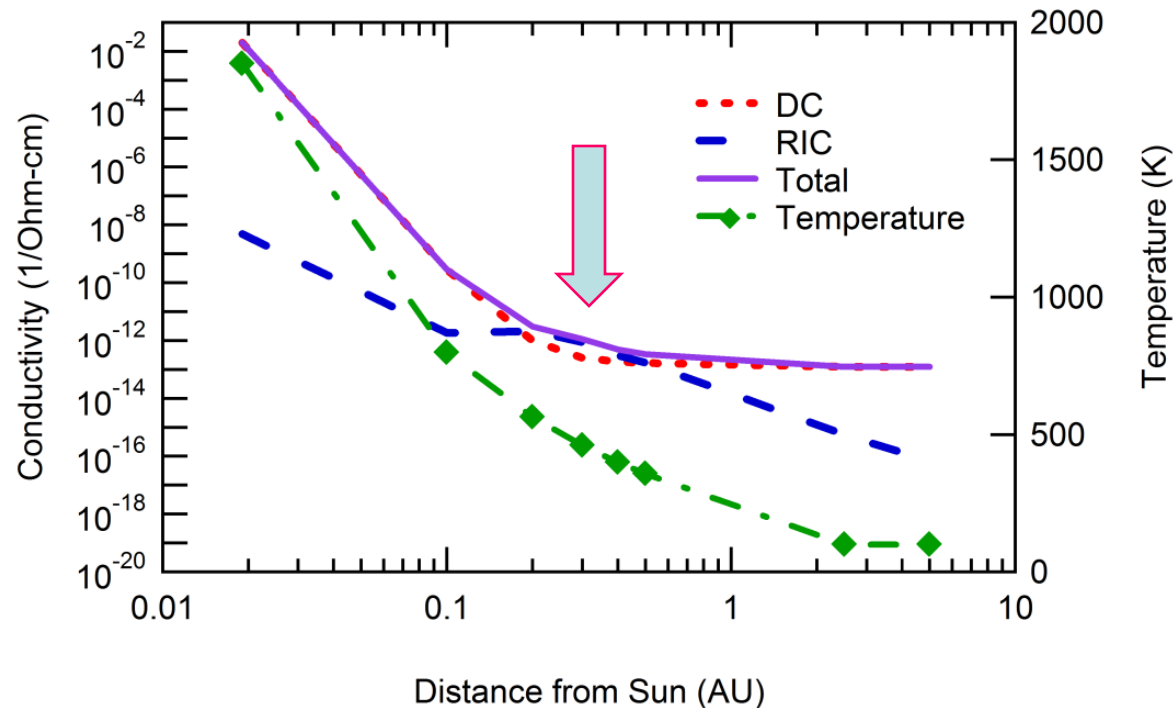
A peak in charging at  
~0.3 to 2 AU

*“...Curiouser and curiouser...”*

--Alice



# Case V: Temperature and Dose Effects



## General Trends

*Dose rate decreases as  $\sim r^2$*   
 *$T$  decreases as  $\sim e^{-r}$*   
 *$\sigma_{DC}$  decreases as  $\sim e^{-1/T}$*   
 *$\sigma_{RIC}$  decreases as  $\sim e^{-1/T}$*   
*and decreases as  $\sim r^2$*

## A fascinating trade-off

- *Charging increases from increased dose rate at closer orbits*
- *Charge dissipation from  $T$ -dependant conductivity increases faster at closer orbits*

# Case VI: Multilayer/Nanocomposite Effects

Consider the Effects of Multilayer Materials, Composites, Contamination, or Oxidation

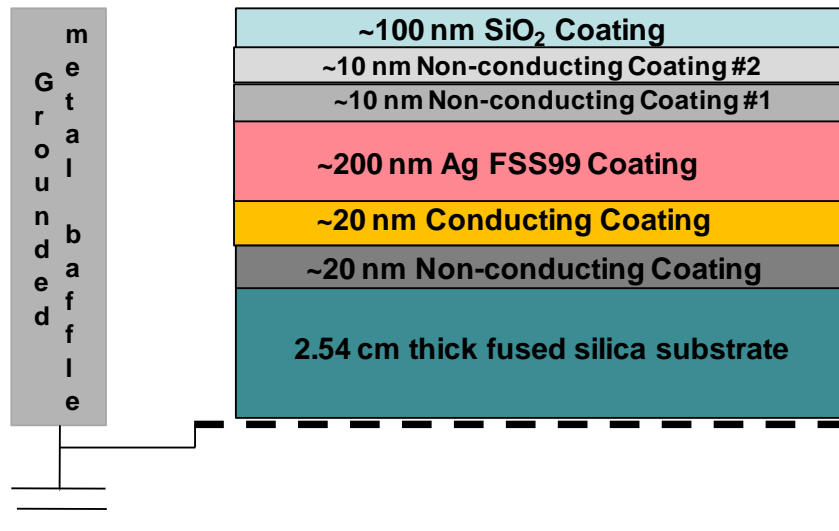
## Length Scale

- Nanoscale structure of materials
- Electron penetration depth
- SE escape depth

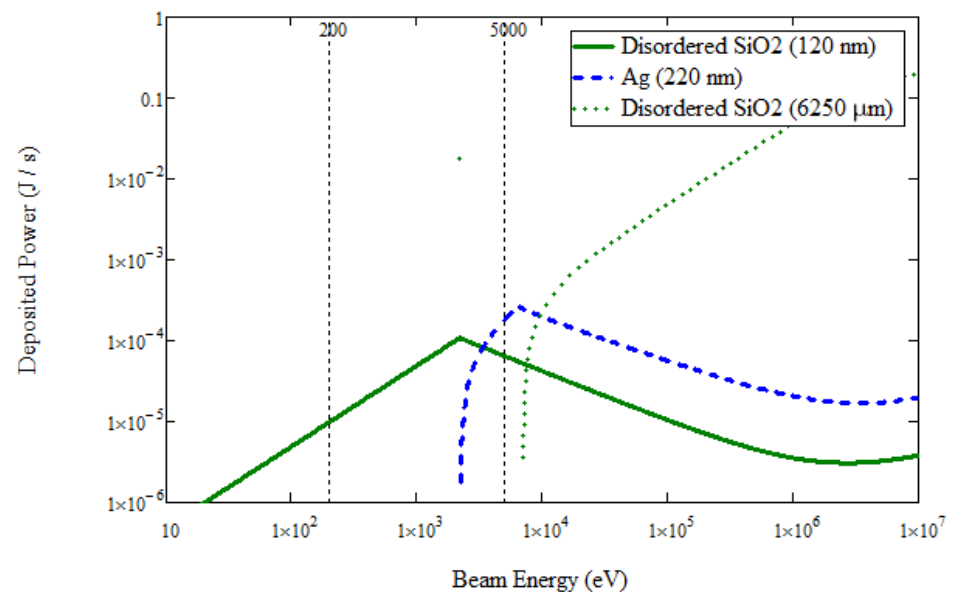
## Time Scales

- Deposition times
- Dissipation times
- Mission duration

## Coated Mirror Structure



## Power Deposition Graph





# Why Does Glow Scale with Flux, Energy and Power?

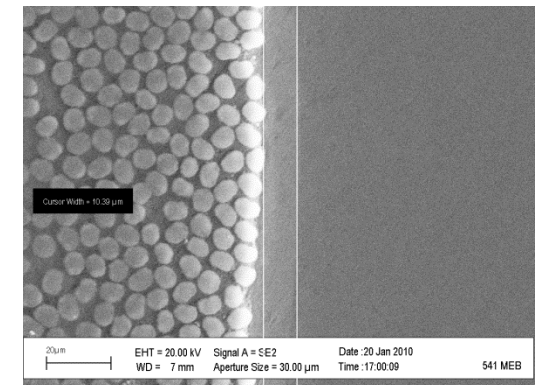
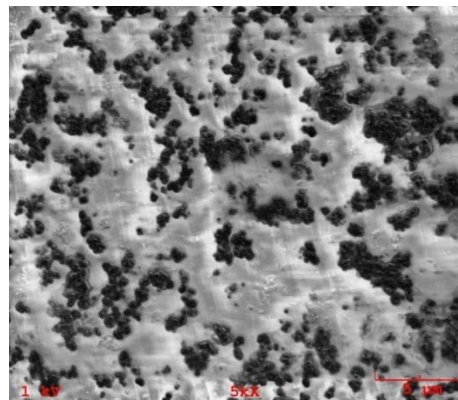
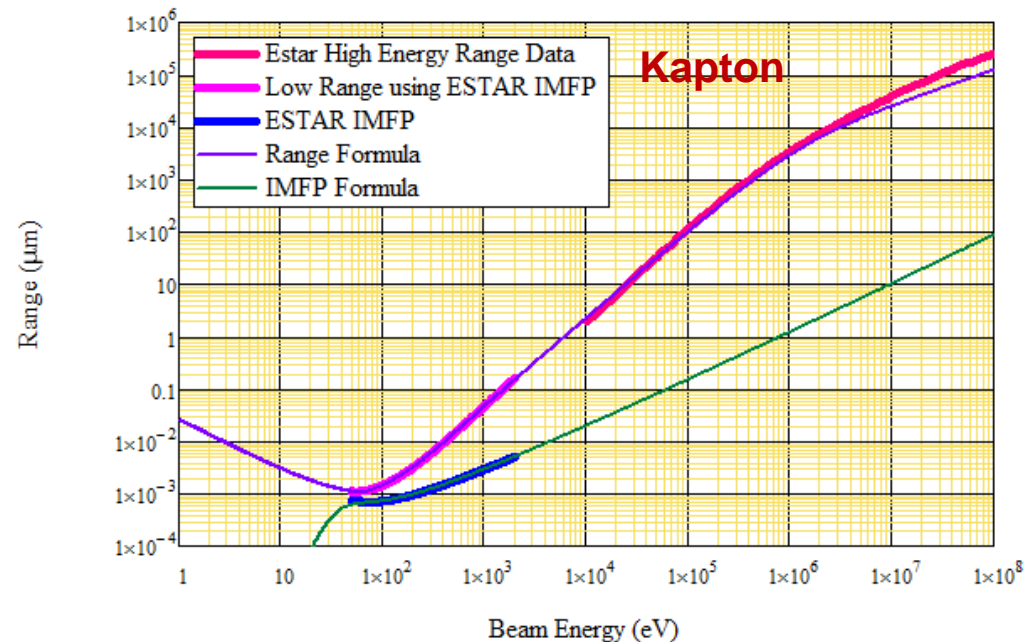
In a simple, but reasonably accurate CSDA, used to model energy loss of electrons traversing solids and their penetration range, the rate of energy loss ( $dE/dz$ ) is assumed constant.

Assuming emission intensity is proportional to energy deposition (dose), emission scales as:

- Incident e-flux, for non-penetrating radiation
- Incident power, for penetrating radiation

Emission scaling depends on sample geometry and materials properties. May lead to:

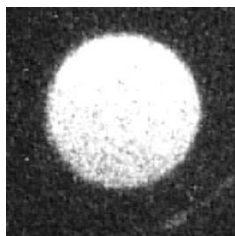
- Power or flux scaling at different incident energies
- Energy or flux thresholds and/or cutoffs
- Significant emission from high energy  $e^-$
- Significant emission from back sides or interior surfaces



10  $\mu\text{m}$

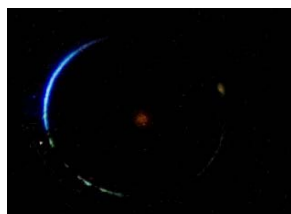
# Diversity of Emission Phenomena in Black Kapton

Ball Black Kapton	22 keV	110 or 4100 $\mu\text{W}/\text{cm}^2$
Runs 131 and 131A	135 K	5 or 188 $\text{nA}/\text{cm}^2$



## Surface Glow

Relatively low intensity  
Always present over full surface when e-beam on  
May decay slowly with time



## Edge Glow

Similar to Surface Glow,  
but present only at sample edge



1



2



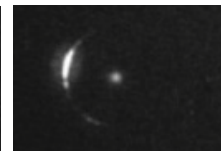
1



2



3



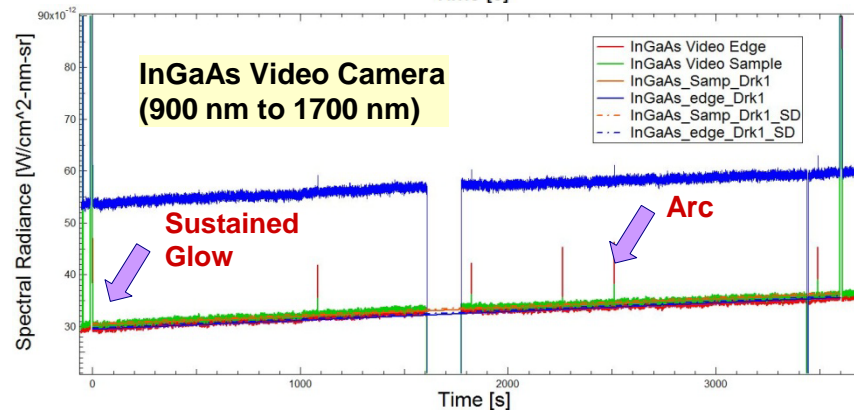
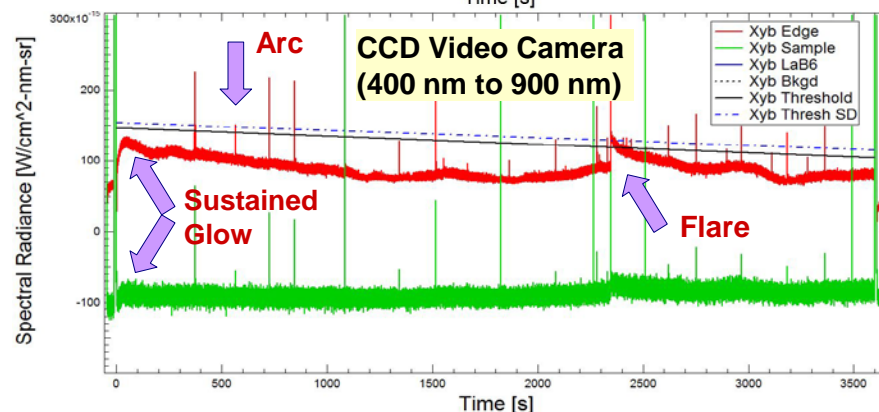
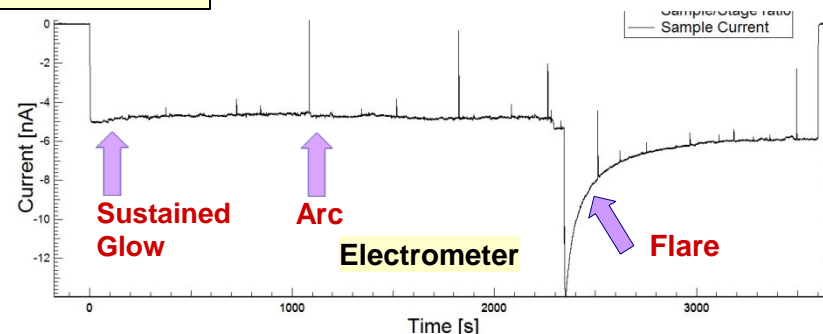
4

## "Flare"

2-20x glow intensity  
Abrupt onset  
2-10 min decay time

## Arc

Relatively very high intensity  
10-1000X glow intensity  
Very rapid <1  $\mu\text{s}$  to 1 s



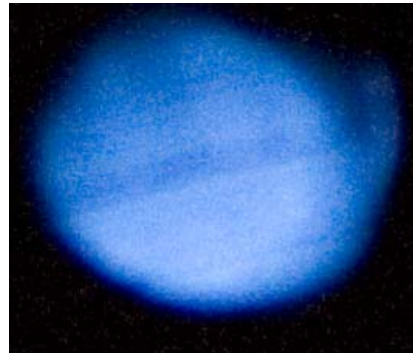
# Glow Increases with Increasing Flux, Energy and Power

$e^-$  Energy

M55J

~110  $\mu\text{W}/\text{cm}^2$   
~5  $\text{nA}/\text{cm}^2$   
22 keV  
135 K

Run 122



M55J

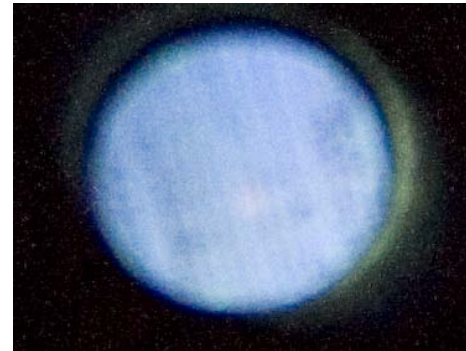
~4100  $\mu\text{W}/\text{cm}^2$   
~188  $\text{nA}/\text{cm}^2$   
22 keV  
135 K

Run 122A

M55J

~35  $\mu\text{W}/\text{cm}^2$   
~5  $\text{nA}/\text{cm}^2$   
7 keV  
128 K

Run 121



M55J

~1300  $\mu\text{W}/\text{cm}^2$   
~188  $\text{nA}/\text{cm}^2$   
7 keV  
128 K

Run 121A

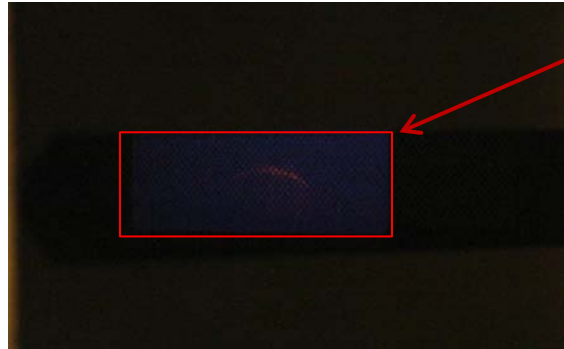
$e^-$  Flux

- Surface Glow, Edge Glow, and Arcing Frequency are all found to increase with increasing incident electron flux and energy.
- Insufficient data for trends to establish functional dependence and possible thresholds or cut-offs



# Emission Increases with Decreasing Temperature

Surface Glow  
**296 K**



Sample Area

Surface Glow  
**294 K**



Surface Glow  
**90 K**



Surface Glow  
**130 K**



## T300 Glow seen at MSFC

Flux density =  $1 \text{ nA/cm}^2$

Energy =  $22 \text{ keV}$

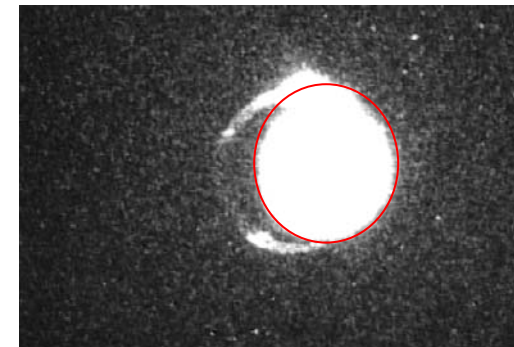
Power  $22 \text{ uW/cm}^2$

Temp =  $296 \text{ K}$  and  $90 \text{ K}$

$$I_{90}/I_{296} \sim 4$$

Similar behavior seen for M55J  
and Black Kapton

“Flare”  
**130 K**



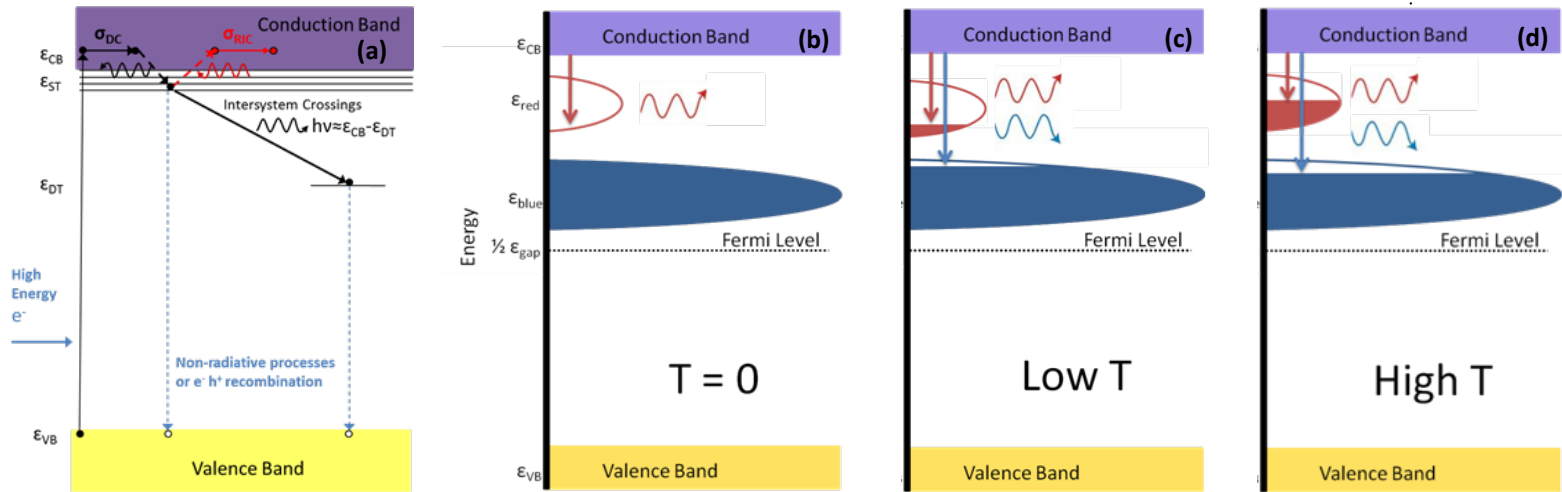
## M55J Glow seen at USU

Flux density =  $5 \text{ nA/cm}^2$

Energy =  $22 \text{ keV}$

Power  $110 \text{ uW/cm}^2$

Temp =  $294 \text{ K}$  and  $130 \text{ K}$

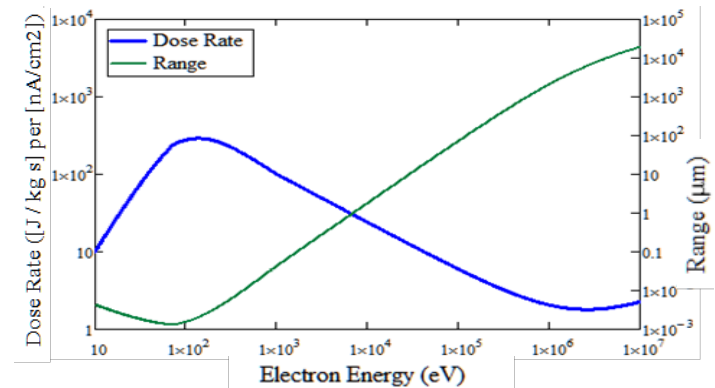


**Fig. 2.** Qualitative two-band model of occupied densities of state (DOS) as a function of temperature during cathodoluminescence. **(a)** Modified Joblonski diagram for electron-induced phosphorescence. Shown are the extended state valence (VB) and conduction (CB) bands, shallow trap (ST) states at  $\epsilon_{ST}$  within  $\sim k_B T$  below the CB edge, and two deep trap (DT) distributions centered at  $\epsilon_{DT} = \epsilon_{red}$  and  $\epsilon_{DT} = \epsilon_{blue}$ . Energy depths are exaggerated for clarity. **(b)** At  $T \approx 0$  K, the deeper DT band is filled, so that there is no blue photon emission if  $\epsilon_{blue} < \epsilon_{eff}$ . **(c)** At low  $T$ , electrons in deeper DT band are thermally excited to create a partially filled upper DT band (decreasing the available DOS for red photon emission) and a partially empty lower DT band (increasing the available DOS for blue photon emission). **(d)** At higher  $T$ , enhanced thermal excitations further decrease red photon emission and increase blue photon emission. Radiation induced

$$I_Y(J_b, E_b, T, \lambda) \propto \dot{D}(J_b, E_b) \left[ \frac{1}{\dot{D} + \dot{D}_{sat}} \left( \frac{\epsilon_{ST}}{k_B T} \right) \right] \{ A_f(\lambda) [1 + \mathbb{R}_m(\lambda)] \} \quad (1)$$

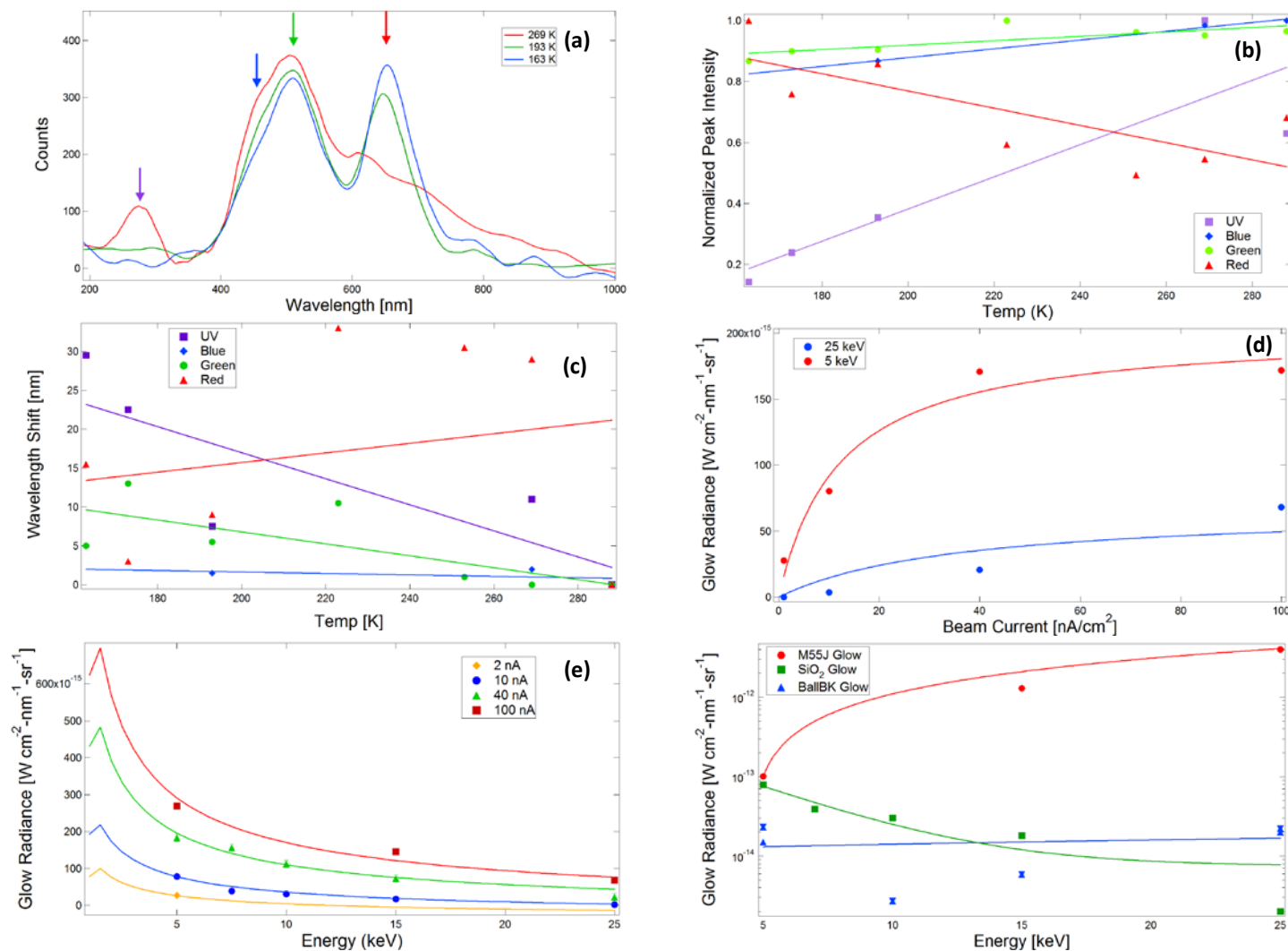
where dose rate  $\dot{D}$  (absorbed power per unit mass) is given by

$$\dot{D}(J_b, E_b) = \frac{E_b J_b [1 - \eta(E_b)]}{q_e \rho_m} \times \begin{cases} [1/L] & ; R(E_b) < L \\ [1/R(E_b)] & ; R(E_b) > L \end{cases} \quad (2)$$



**Fig. 3.** Range and dose rate of disordered SiO<sub>2</sub> as a function of incident energy using calculation methods and the continuous slow-down approximation described in [5].



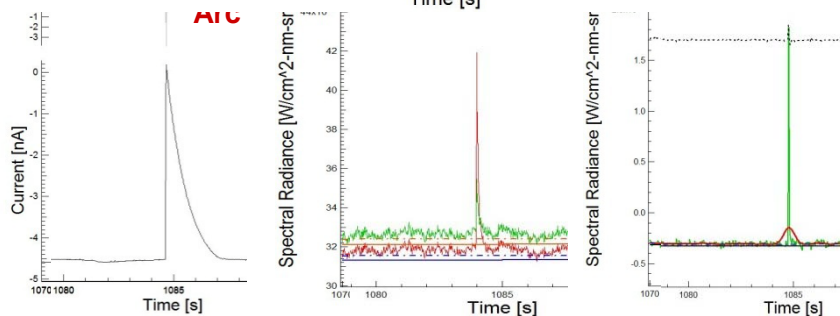
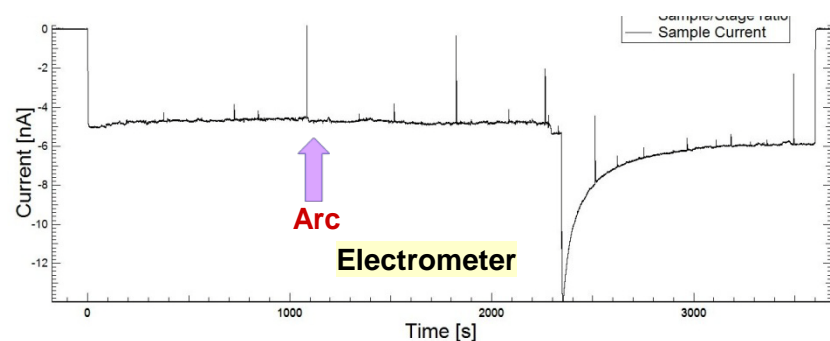


**Fig. 1.** Optical measurements of luminescent thin film disordered SiO<sub>2</sub> samples. **(a)** Three luminescence UV/VIS spectra at decreasing sample temperature. Four peaks are identified: red (~645 nm), green (~500 nm), blue (~455 nm) and UV (275 nm). **(b)** Peak amplitudes as a function of sample temperature, with baseline subtracted and normalized to maximum amplitudes. **(c)** Peak wavelength shift as a function of sample temperature. **(d)** Total luminescent radiance versus beam current at fixed incident energy fit by (1). **(e)** Total luminescent radiance versus beam energy at fixed incident flux fit by (1). **(f)** Total luminescent radiance versus beam energy at fixed 10 nA/cm<sup>2</sup> incident flux for epoxy-resin M55J carbon composite (red; linear fit), SiO<sub>2</sub> coated mirror (green; fit with (1)), and



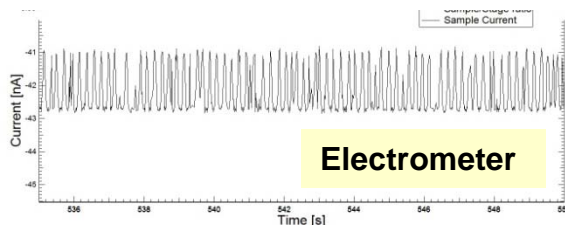
# Arcs Observed in Black Kapton and M55J

Ball Black Kapton 22 keV 110 or 4100  $\mu\text{W}/\text{cm}^2$   
Runs 131 and 131A 135 K 5 or 188  $\text{nA}/\text{cm}^2$



Electrometer InGaAs Video CCD Video

Rapid Arcing at  
4  $\text{mW}/\text{cm}^2$   
~20000 arcs/hr

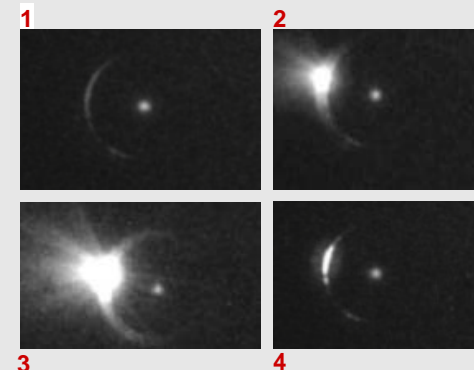


## Arc Characteristics

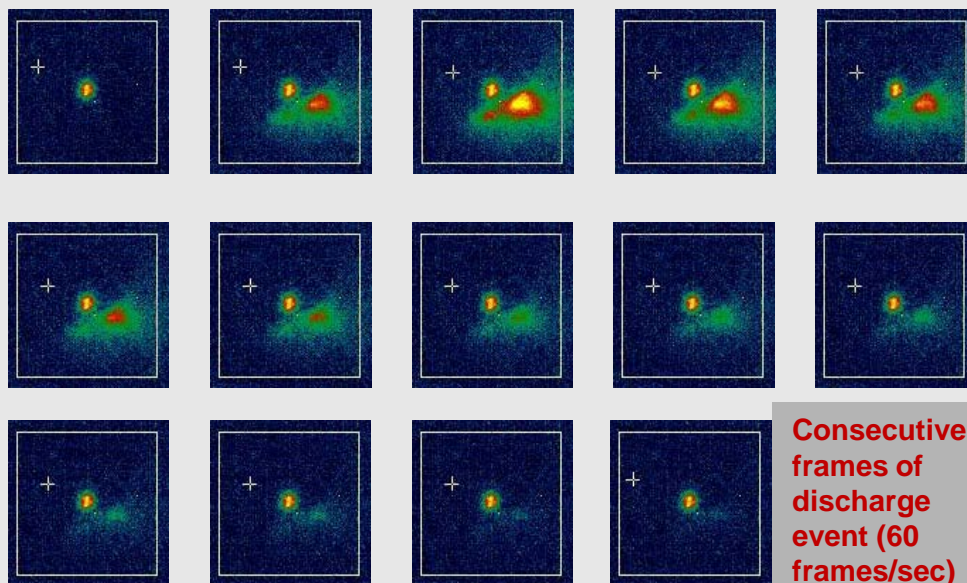
Arc duration:  
~0.2 to 0.8 s in electrometers  
and video cameras

Arc Freq. at 110  $\mu\text{W}/\text{cm}^2$  :  
~10 arcs/hr for Black Kapton  
~30 arcs/hr for M55J

Arc Intensity:  
~ 10X to 1000X glow amplitude  
~5% to 20% of glow power



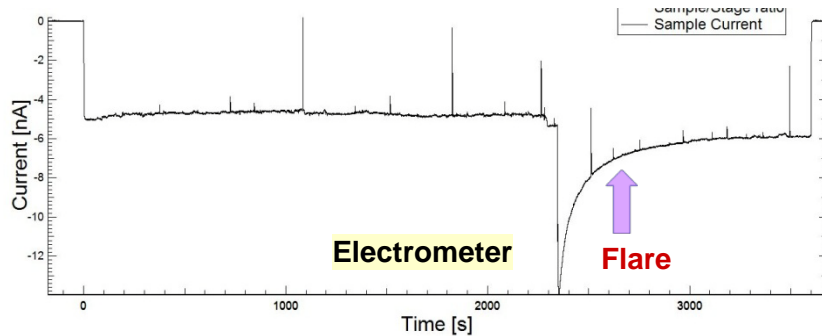
CCD camera (400nm-900nm)



Consecutive  
frames of  
discharge  
event (60  
frames/sec)

InGaAs camera (900nm-1700nm)

# “Flares” Observed in Black Kapton



Ball Black Kapton

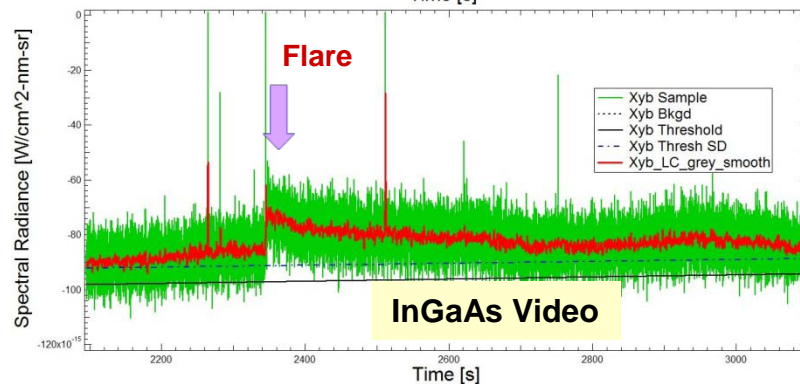
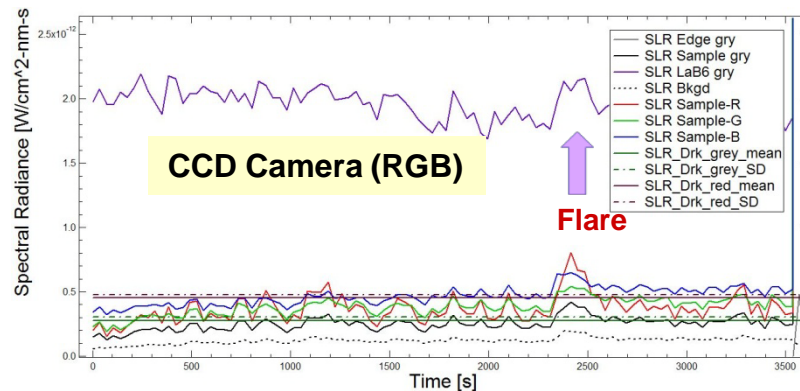
Runs 131

110  $\mu\text{W}/\text{cm}^2$

5  $\text{nA}/\text{cm}^2$

22 keV

135 K



## “Flare” Characteristics

“Flare” duration:

Abrupt onset

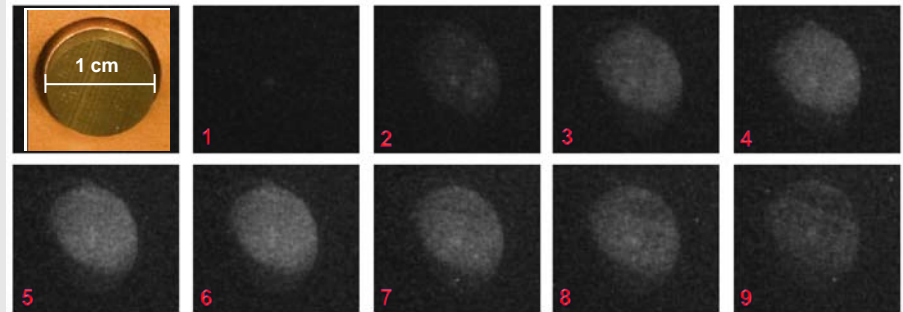
~2-10 min exp. decay time  
in electrometers and video  
cameras

“Flare” Frequency:

0-2 flares/hr

“Flare” Intensity:

~ 2X to 20X glow amplitude  
~5% to 20% of glow power



CCD camera  
(400nm-900nm)

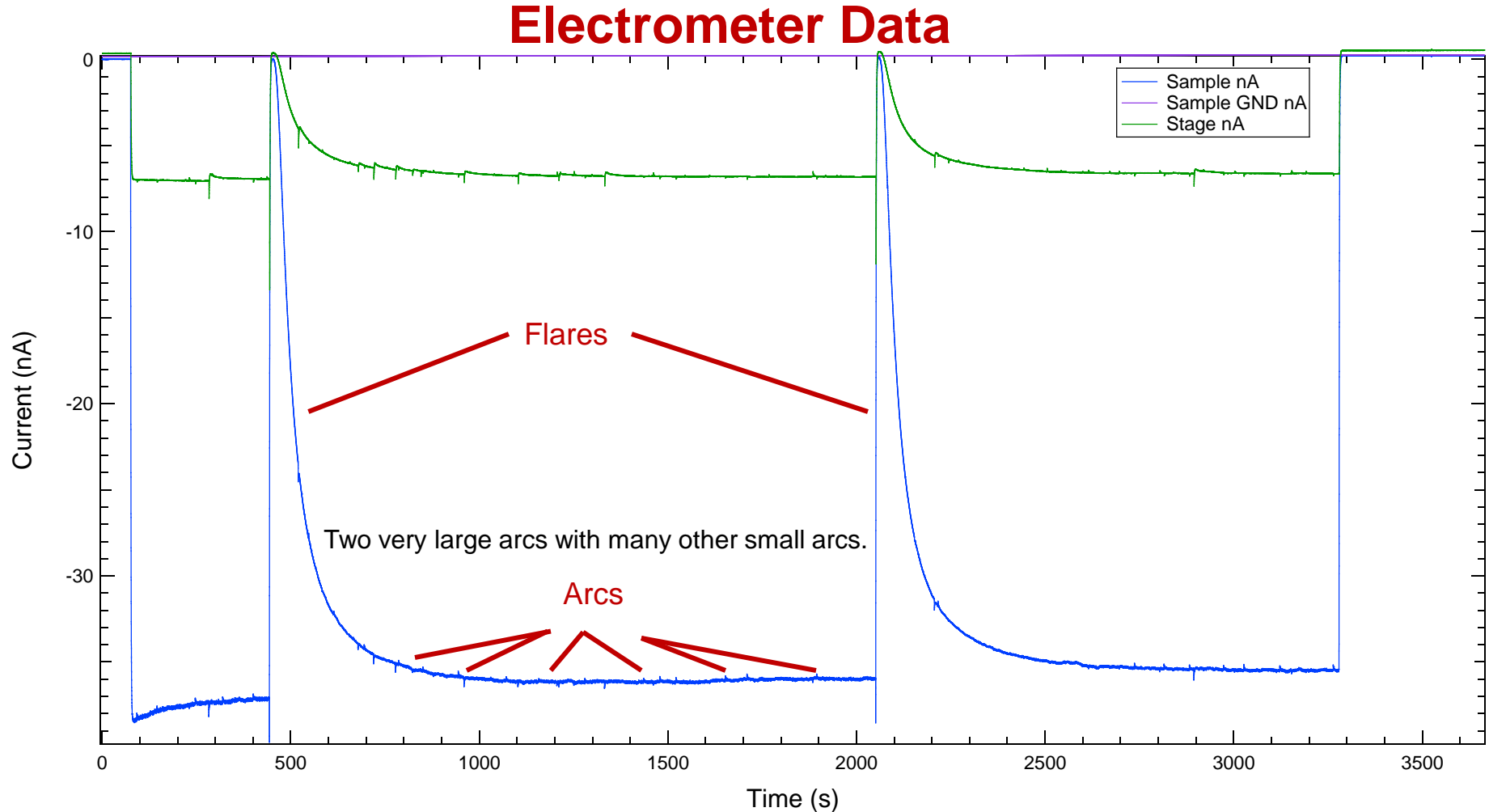
M55J

5  $\text{nA}/\text{cm}^2$

22 keV

135 K

# Details of Electrometer “Flare” Signature



Total Beam Time: 3204 s  
# of Arcs: >50

**High Conductivity  
C-loaded Kapton  
25keV 38nA ~1 hr**

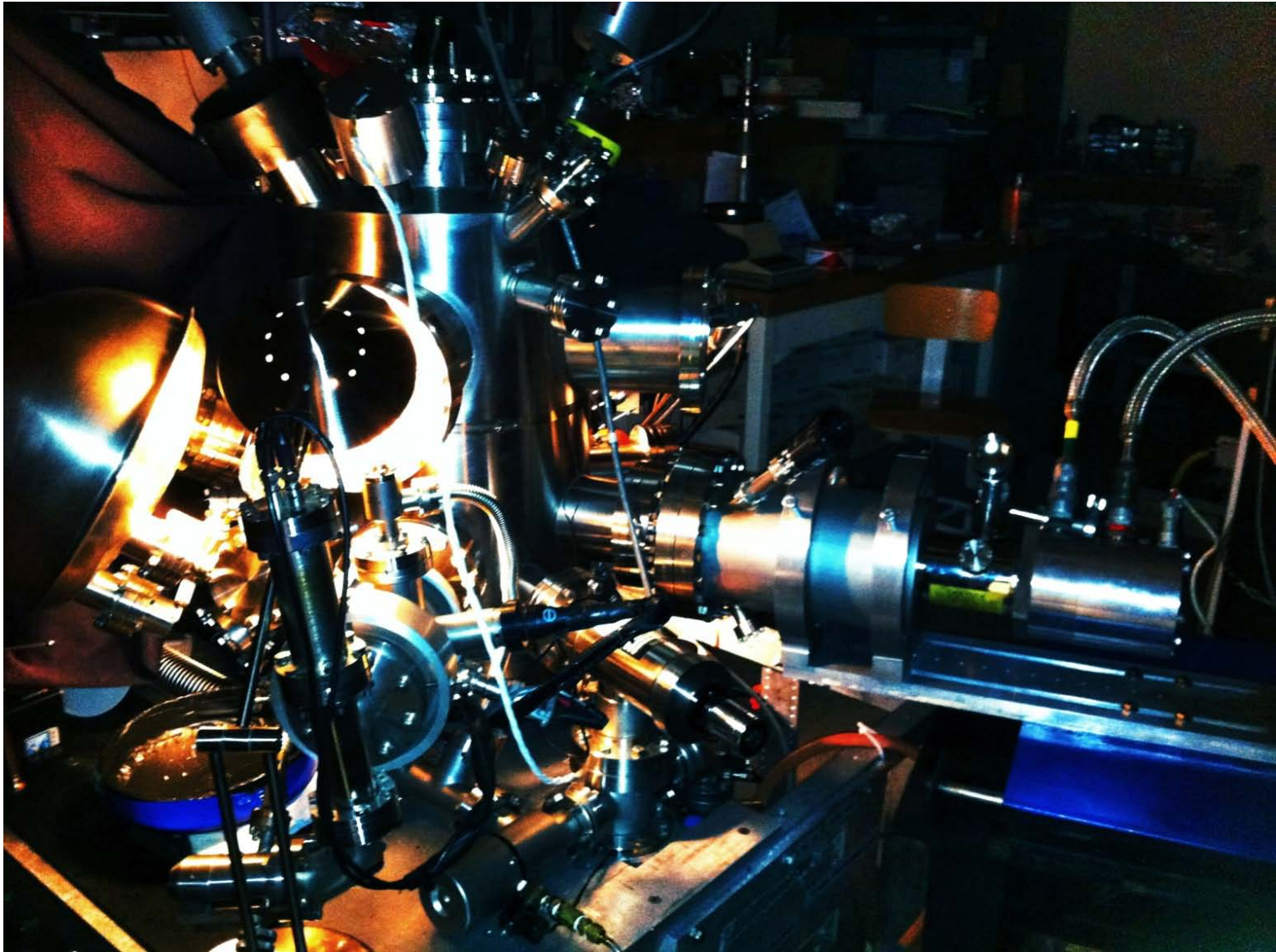


# Conclusions

- Complex satellites require:
  - Complex materials configurations
  - More power
  - Smaller, more sensitive devices
  - More demanding environments
- There are numerous clear examples where **accurate dynamic charging models** require **accurate dynamic materials properties**
- It is not sufficient to use static (BOL or EOL) materials properties
- Environment/Materials Modification feedback mechanisms can cause many new problems
- Use available modeling tools with broader materials knowledgebase and a conscious awareness of the dynamic nature of materials to foresee and mitigate potential spacecraft charging problems



# End with a Bang

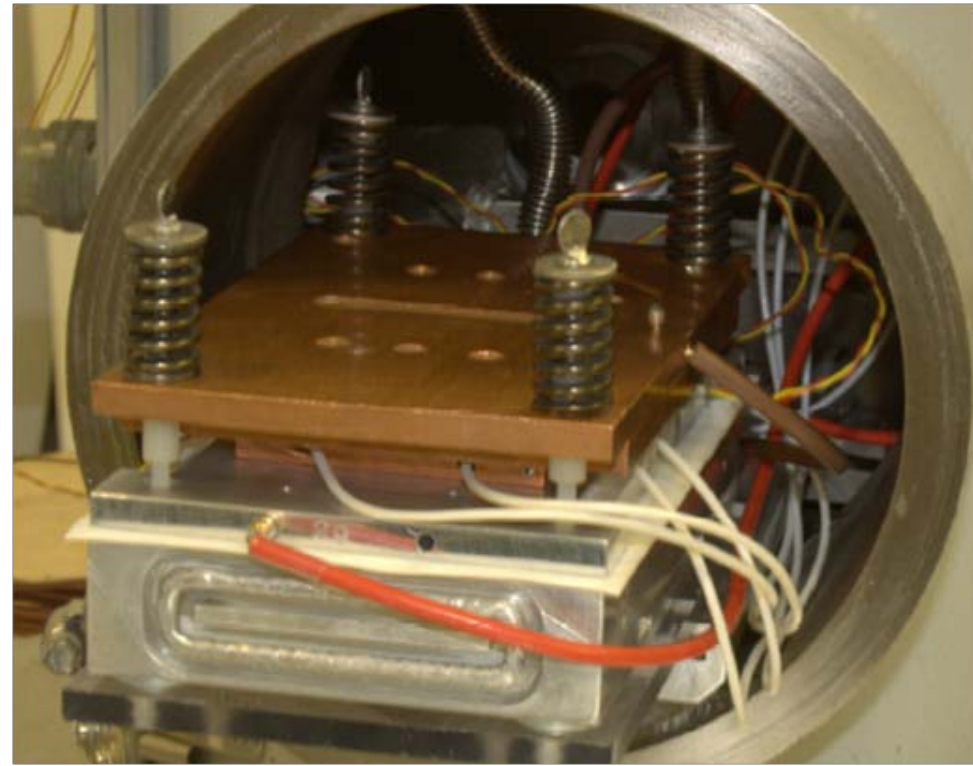
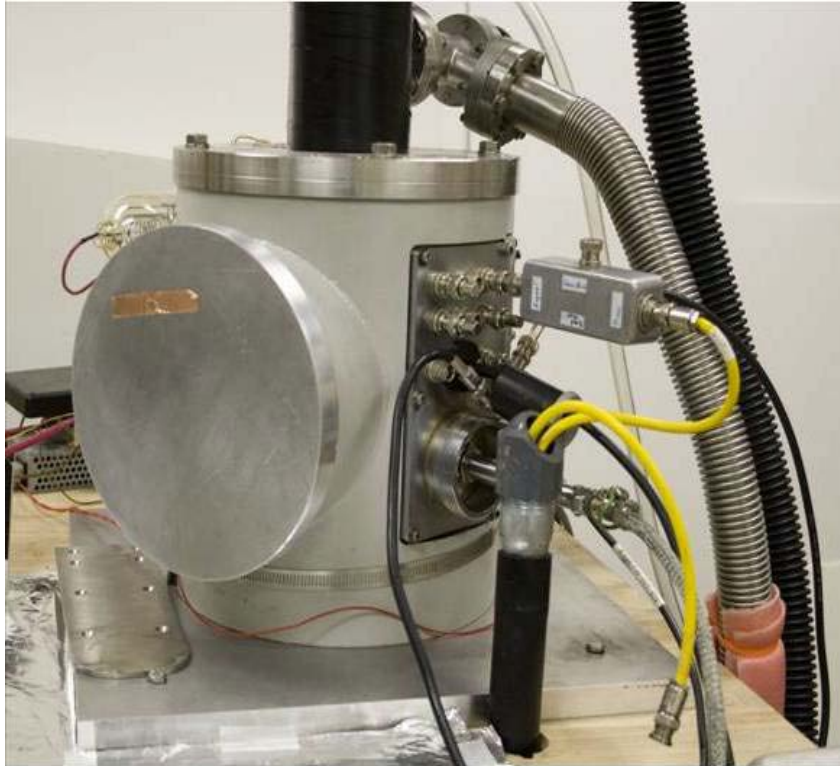


# Supplemental Slides

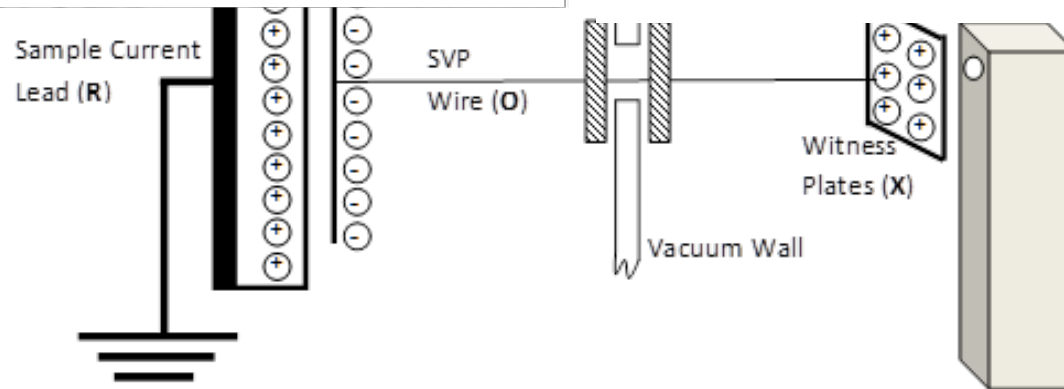
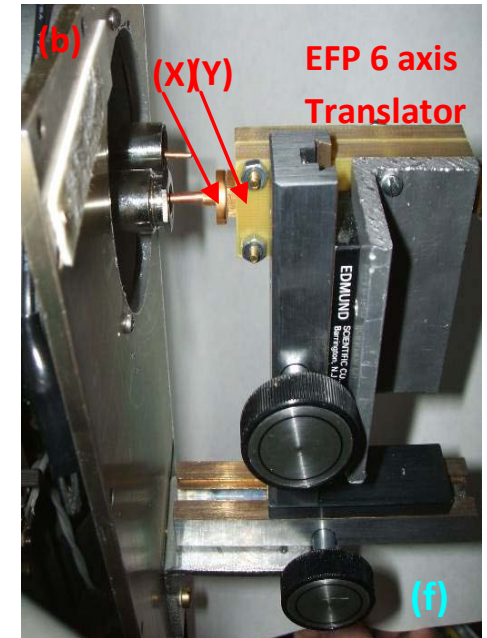
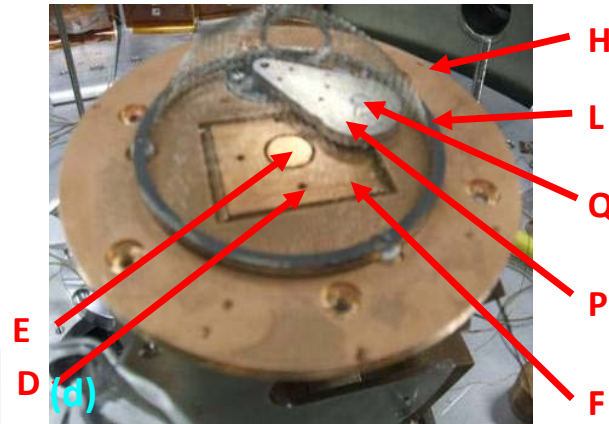
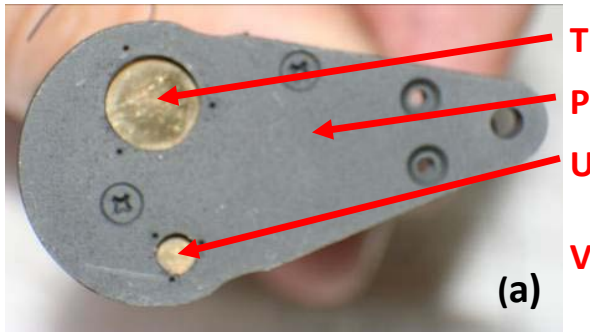
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# Extremely Low Conductivity



# Surface Voltage



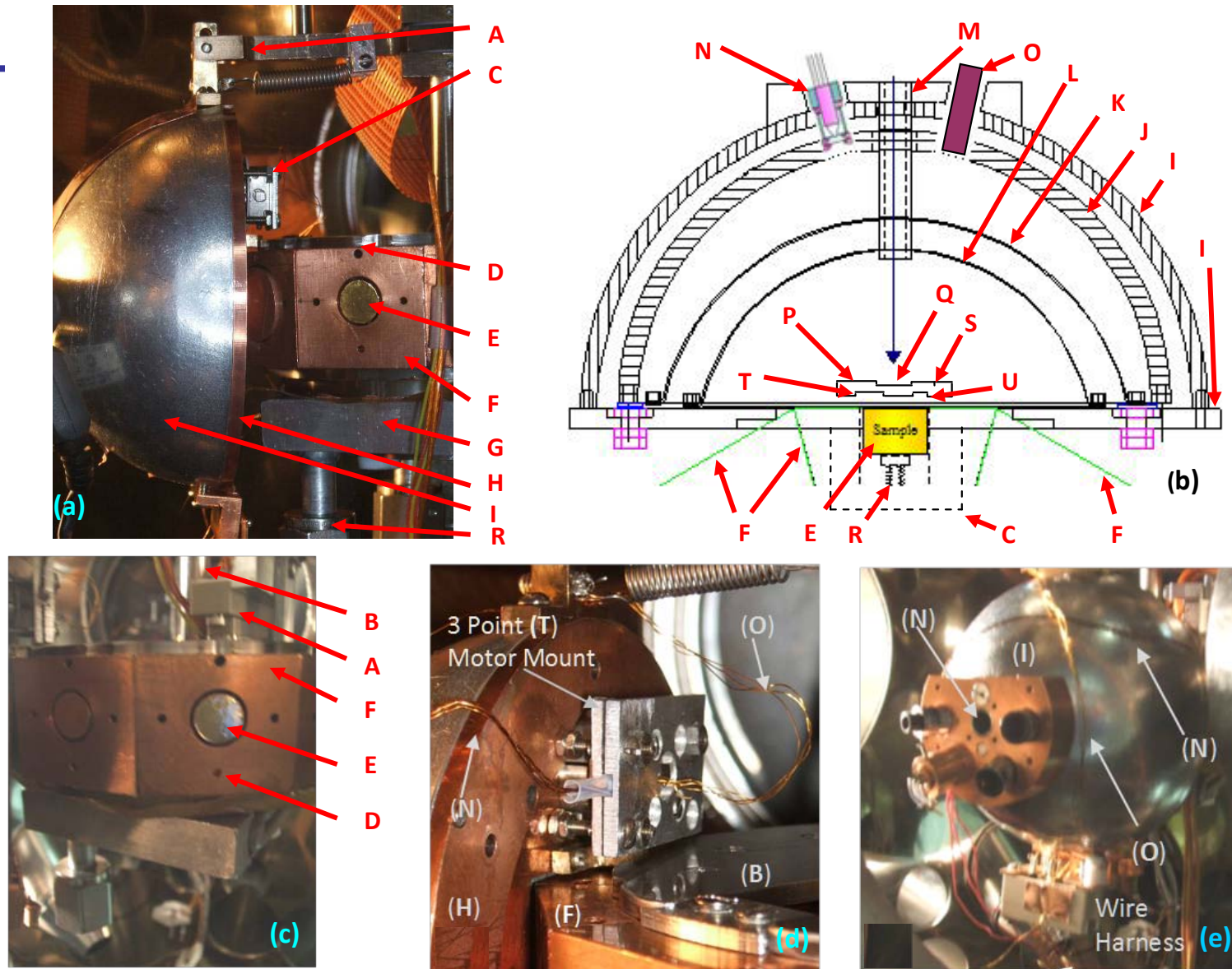
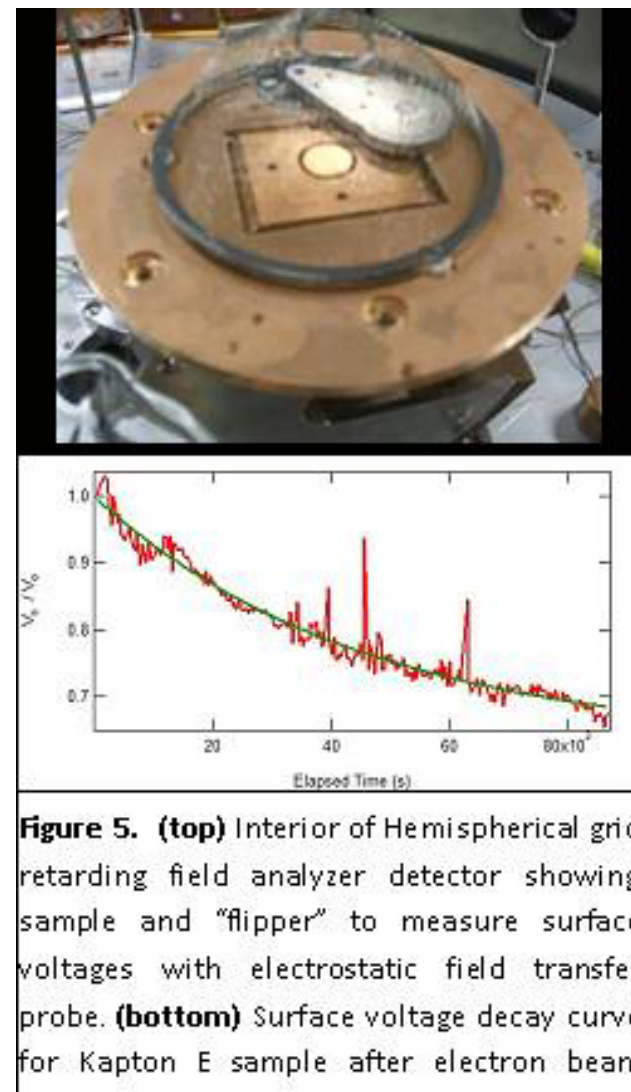
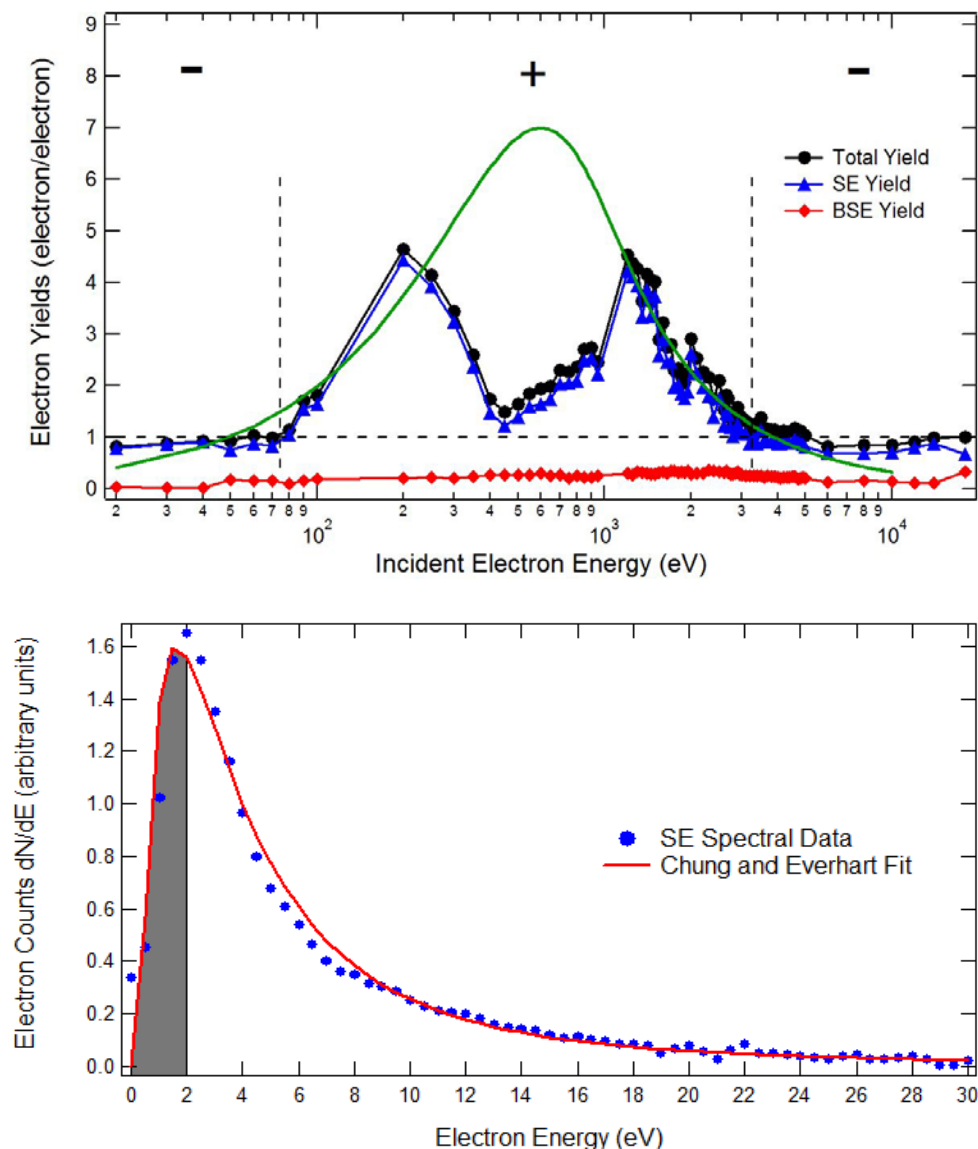


Fig. 2. Hemispherical Grid Retarding Field Analyzer (HGRFA). (a) Photograph of sample stage and HGRFA detector (side view). (b) Cross section of HGRFA. (c) Photograph of sample stage showing sample and cooling reservoir. (d) Side view of the mounting of the stepper motor. (e) Isometric view of the HGRFA detailing the flood gun, optical ports, and wire harness.

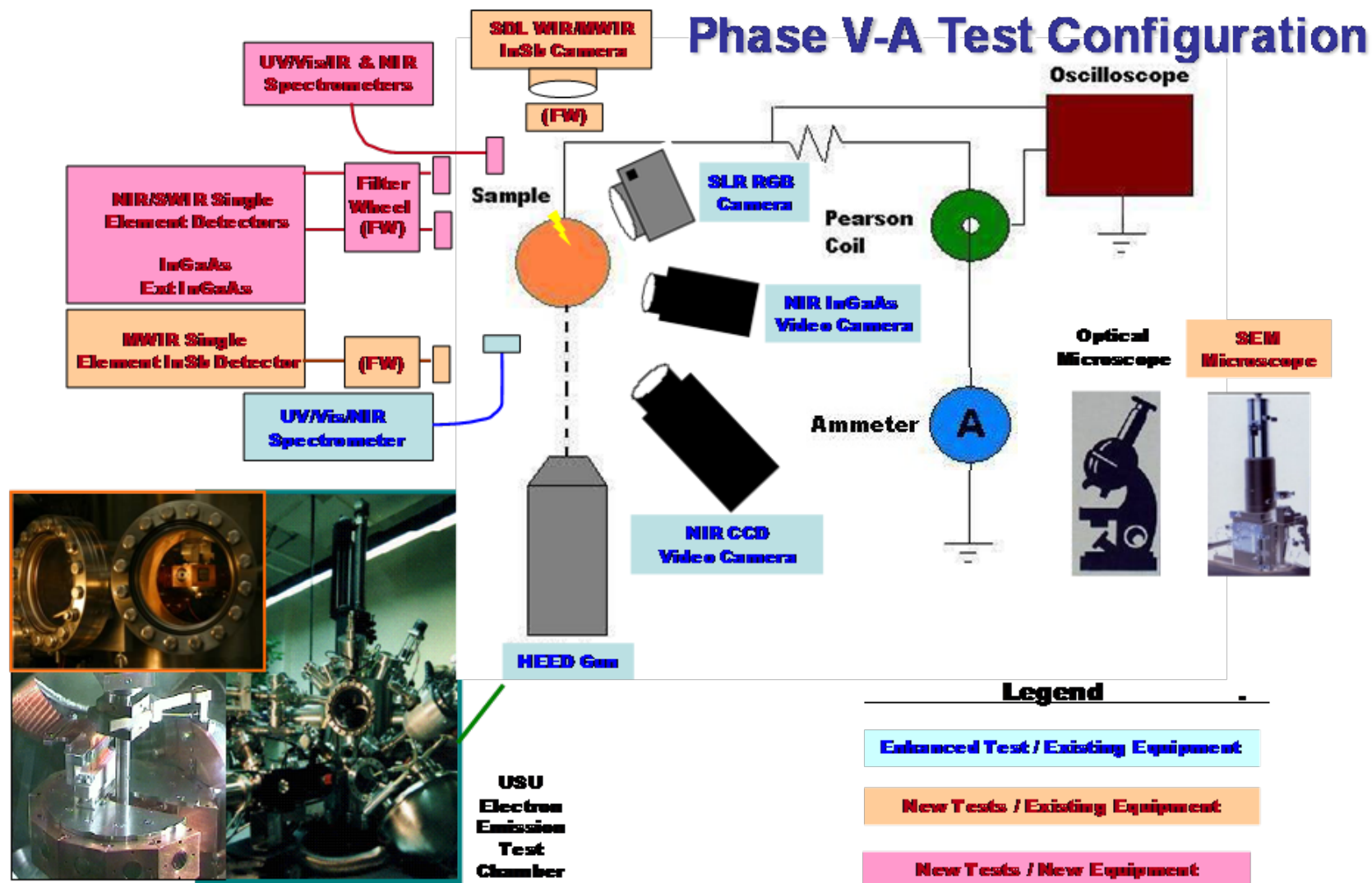


# Low Charge Capabilities



**Figure 5. (top)** Interior of Hemispherical grid retarding field analyzer detector showing sample and "flipper" to measure surface voltages with electrostatic field transfer probe. **(bottom)** Surface voltage decay curve for Kapton E sample after electron beam

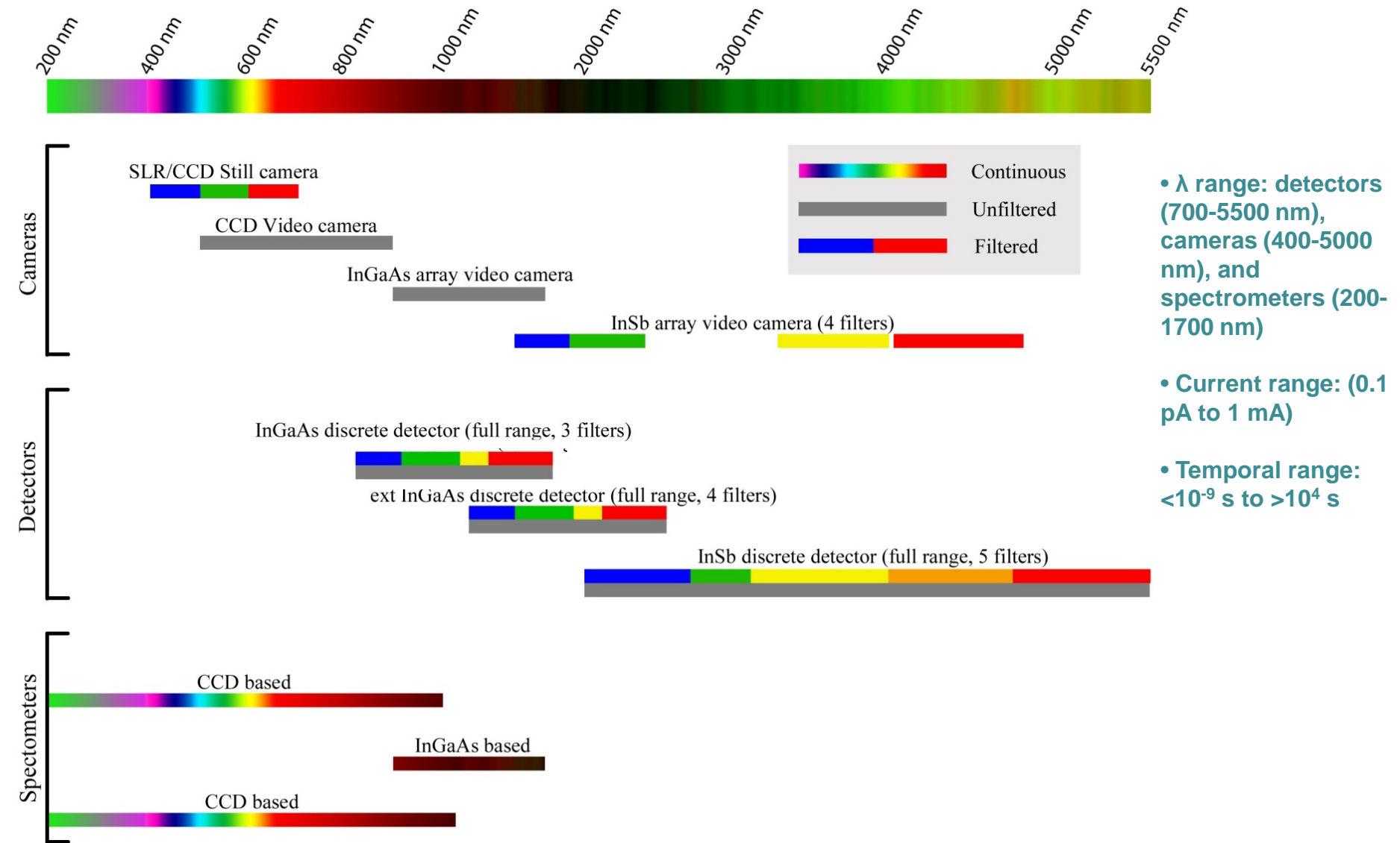
# Luminescence/Arc/Flare Test Configuration



Sample cooled with I-N<sub>2</sub> to 100-135 K.  
Chamber walls at ambient.



# Luminescence/Arc/Flare Test Configuration



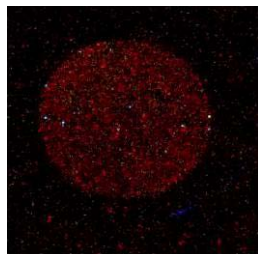


# Comparison of Luminescence Images

## Sustained Glow

Kapton XC

500 nA/cm<sup>2</sup>  
22 keV  
150 K



M55J

1 nA/cm<sup>2</sup>  
22 keV  
100 K



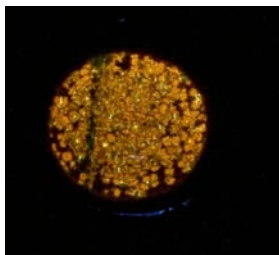
IEC Shell Face  
Epoxy Resin with  
Carbon Veil

1 nA/cm<sup>2</sup>  
22 keV  
100 K



Kapton E

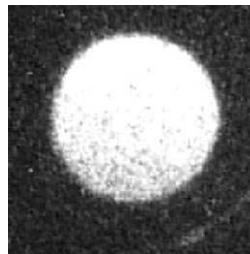
500 nA/cm<sup>2</sup>  
22 keV  
150 K



## "Flare"

Kapton XC

50 nA/cm<sup>2</sup>  
22 keV  
150 K



M55J

1 nA/cm<sup>2</sup>  
22 keV  
100 K



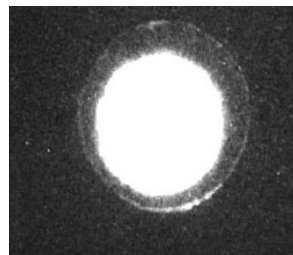
IEC Shell Face  
Epoxy Resin  
with Carbon Veil

1 nA/cm<sup>2</sup>  
22 keV  
100 K



Kapton E

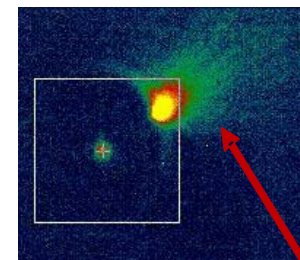
5 uA/cm<sup>2</sup>  
22 keV  
150 K



## Arcs

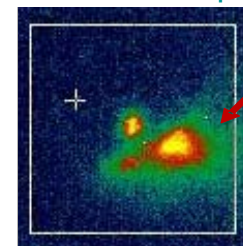
Kapton XC

5 nA/cm<sup>2</sup>  
22 keV  
1350 K



M55J

5 nA/cm<sup>2</sup>  
22 keV  
135 K



IEC Shell Face  
Epoxy Resin  
with Carbon Veil

5 nA/cm<sup>2</sup>  
22 keV  
100 K



Arc

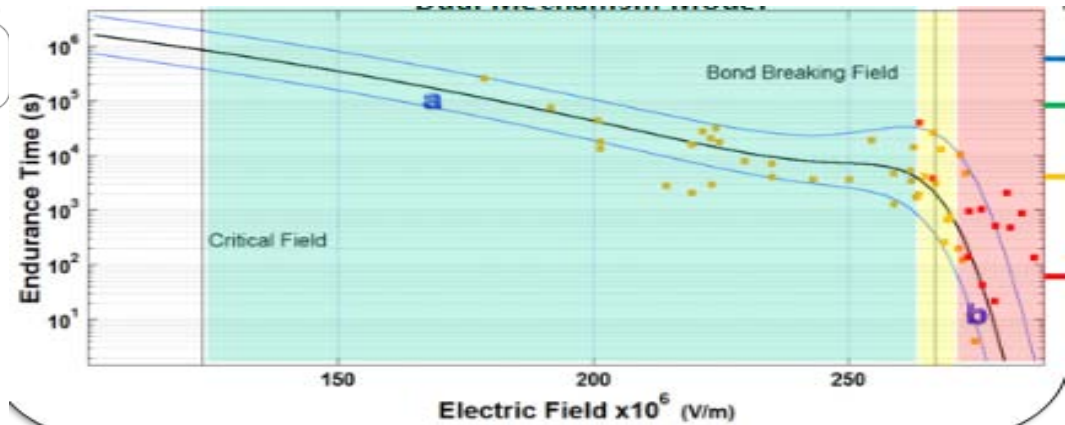
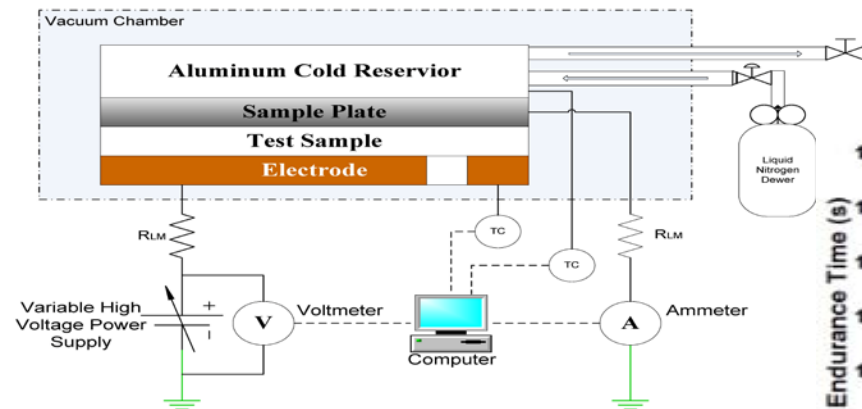
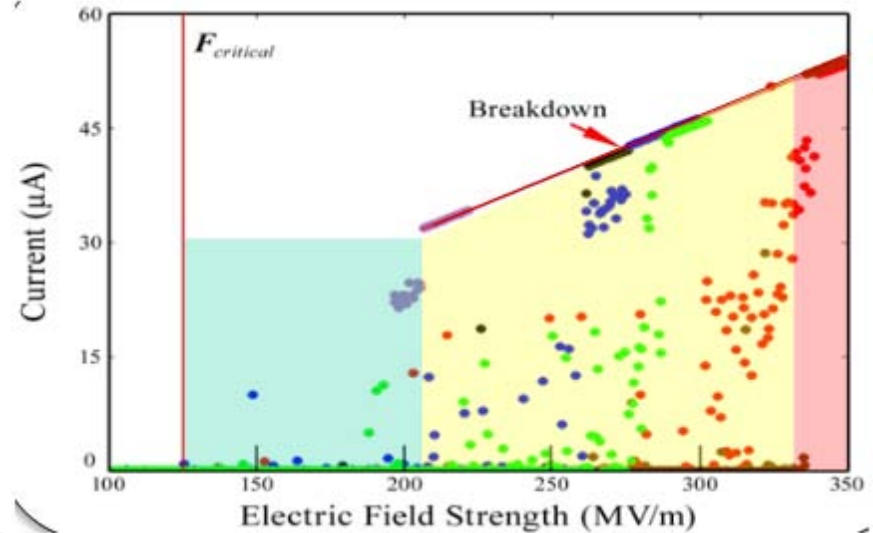
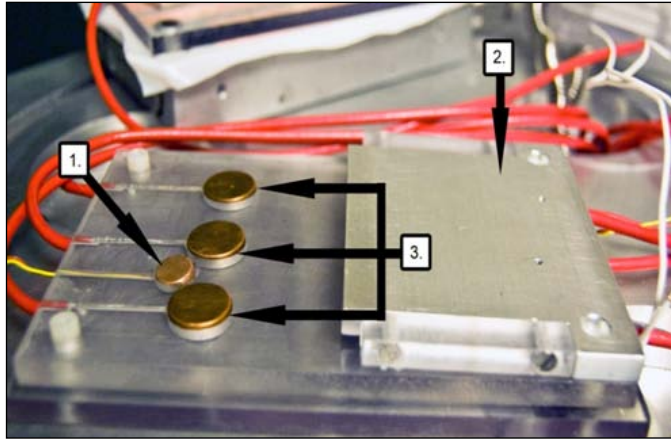
1 cm Dia test samples

30 s Exposure SLR Camera  
(400nm-640nm)

33 ms Exposure CCD Video Camera  
(500nm-900nm)

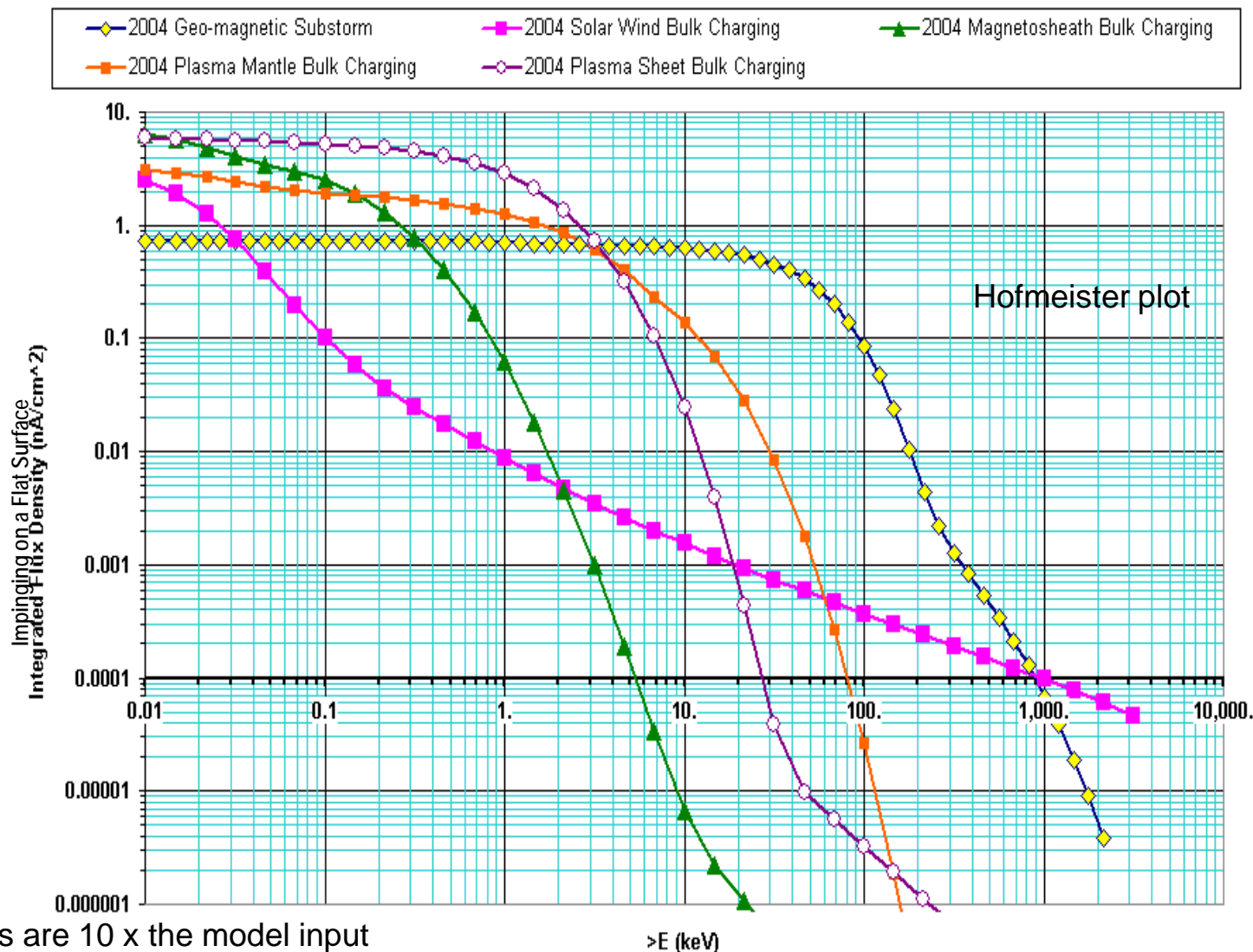
17 ms Exposure InGaAs Video Camera  
(900nm-1700nm)

# Electrostatic Breakdown



# EV Spec worst case (Minow)

## 2004 GEO and L2 Bulk Charging Environments - Electrons

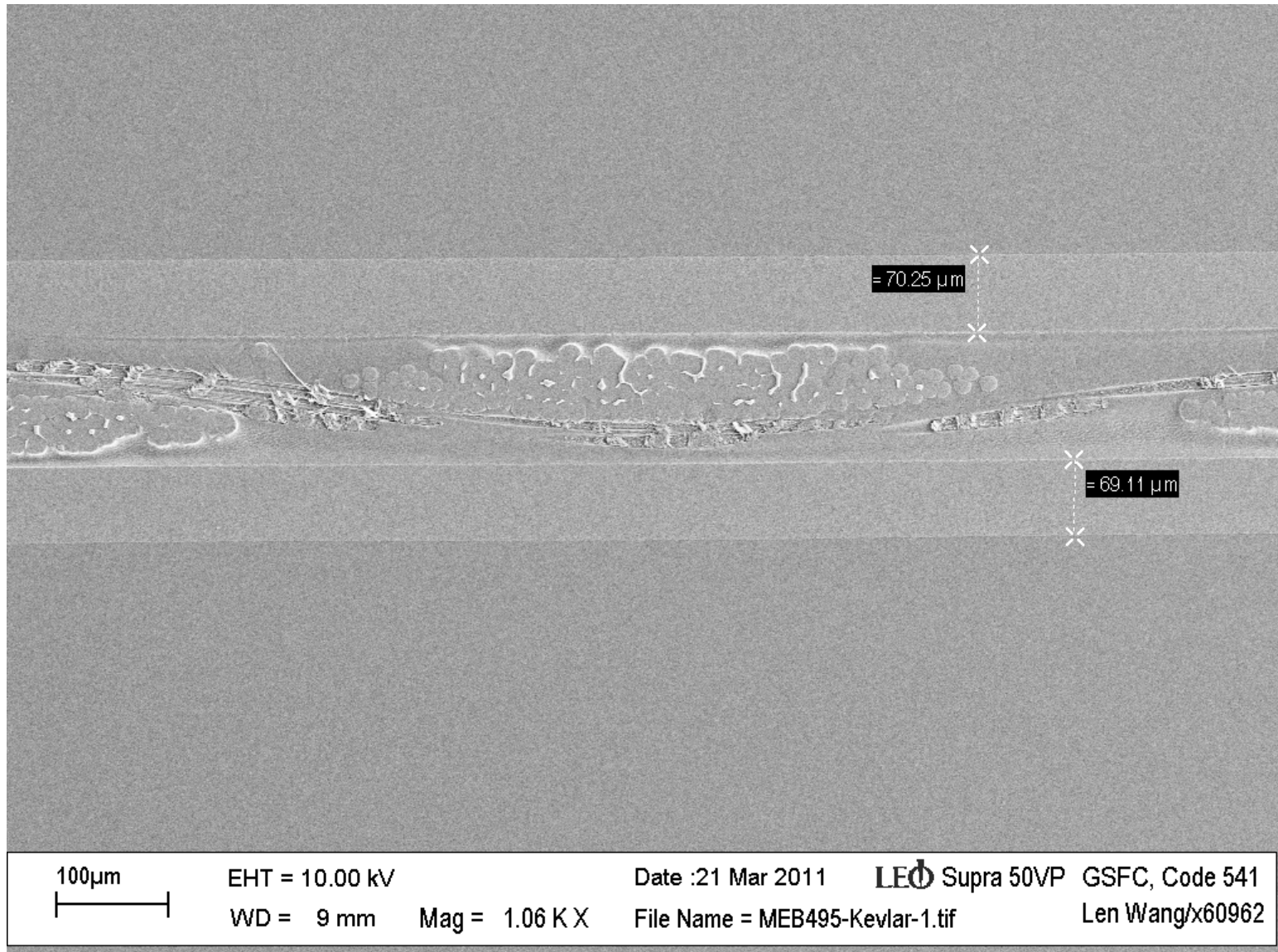


These values are 10 x the model input values, adjusted in the model per recent Geotail and WIND data

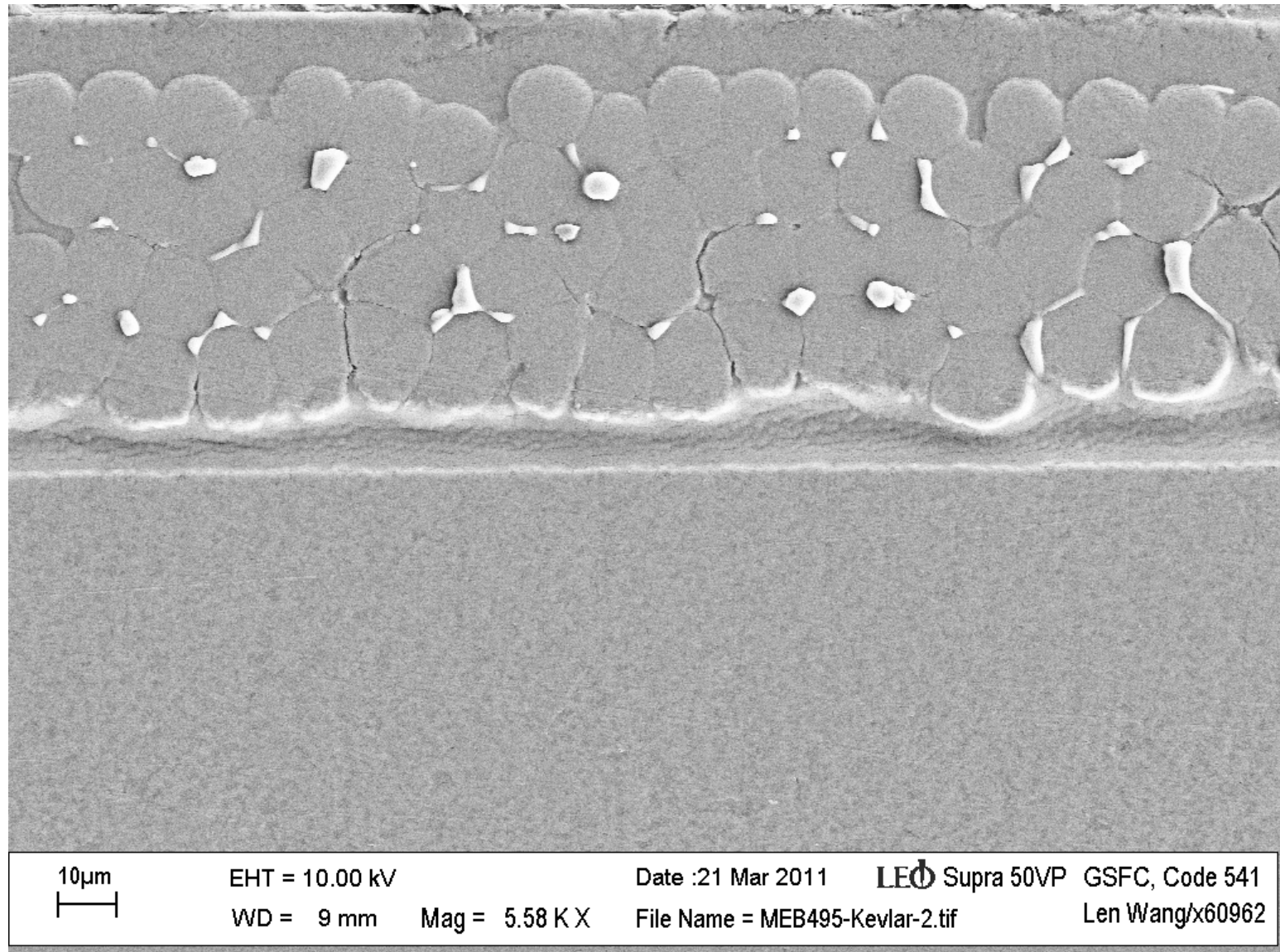
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# Ball Kapton/Kevlar Composite—SEM Inspection (GSFC)



Sample 275XC/Kevlar/275XC cross section view



Sample 275XC/Kevlar/275XC cross section view